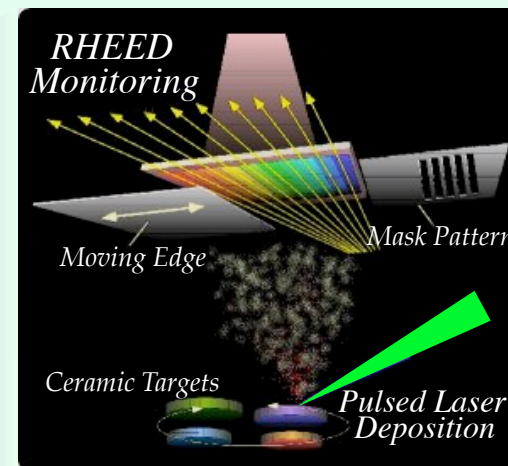
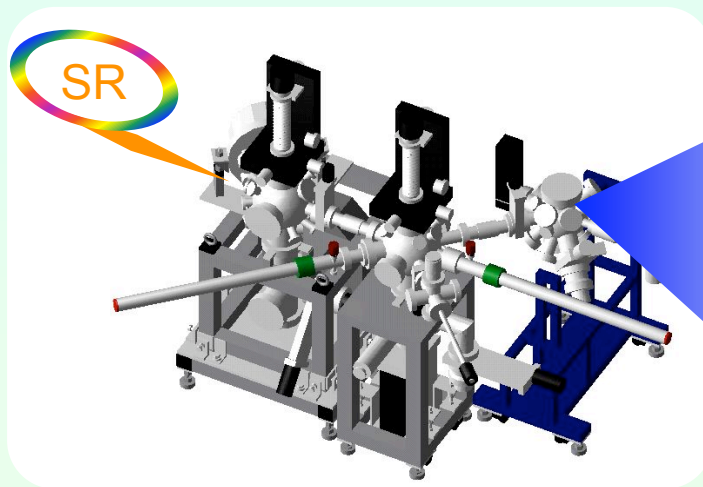


ISSP Workshop「東京大学アウトステーション(SPring-8 BL07LSU)での物性
研究の新展開」 2011年3月8日@ISSP 6F第一会議室

放射光電子分光を用いた 酸化物超構造の電子状態研究

東京大学大学院工学系研究科
JST-さきがけ
東京大学放射光連携研究機構

組頭 広志



共同研究者



次元性制御SrVO₃&LaNiO₃薄膜@BL2C

東大院工

吉松公平、坂井延寿*、堀場弘司*、豊田智史*、尾嶋 正治*

東大院理

藤森淳

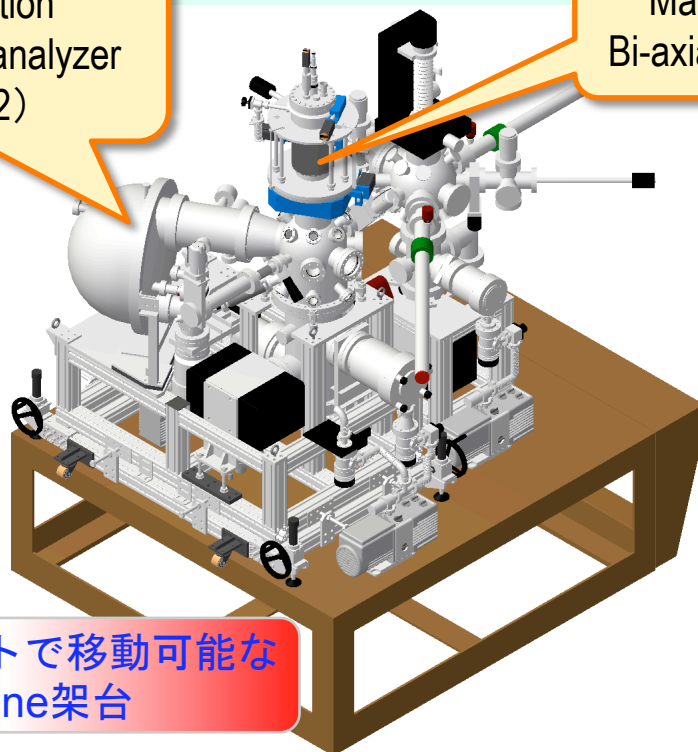
オークリッジ国立研

岡本敏史

*JST-CREST、#東大放射光機構

High-resolution
photoemission analyzer
(SES2002)

Manipulator with
Bi-axial rotating stage



エネルギー分解能 (Total)

: $E/\Delta E = 10,000$

角度分解能: $< 0.1^\circ$

試料温度: 10 ~ 400 K

二軸試料角度走査

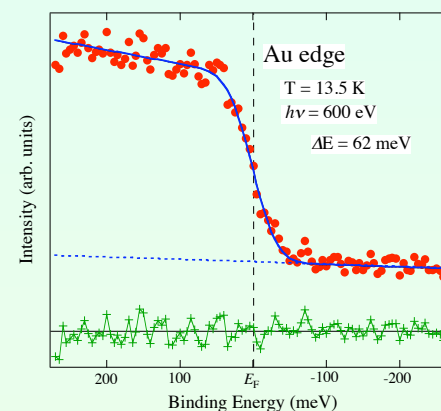
フェルミ面 mapping、LD-XAS



BL2C

300–1500 eV

ホバークラフトで移動可能な
All-in-one 架台



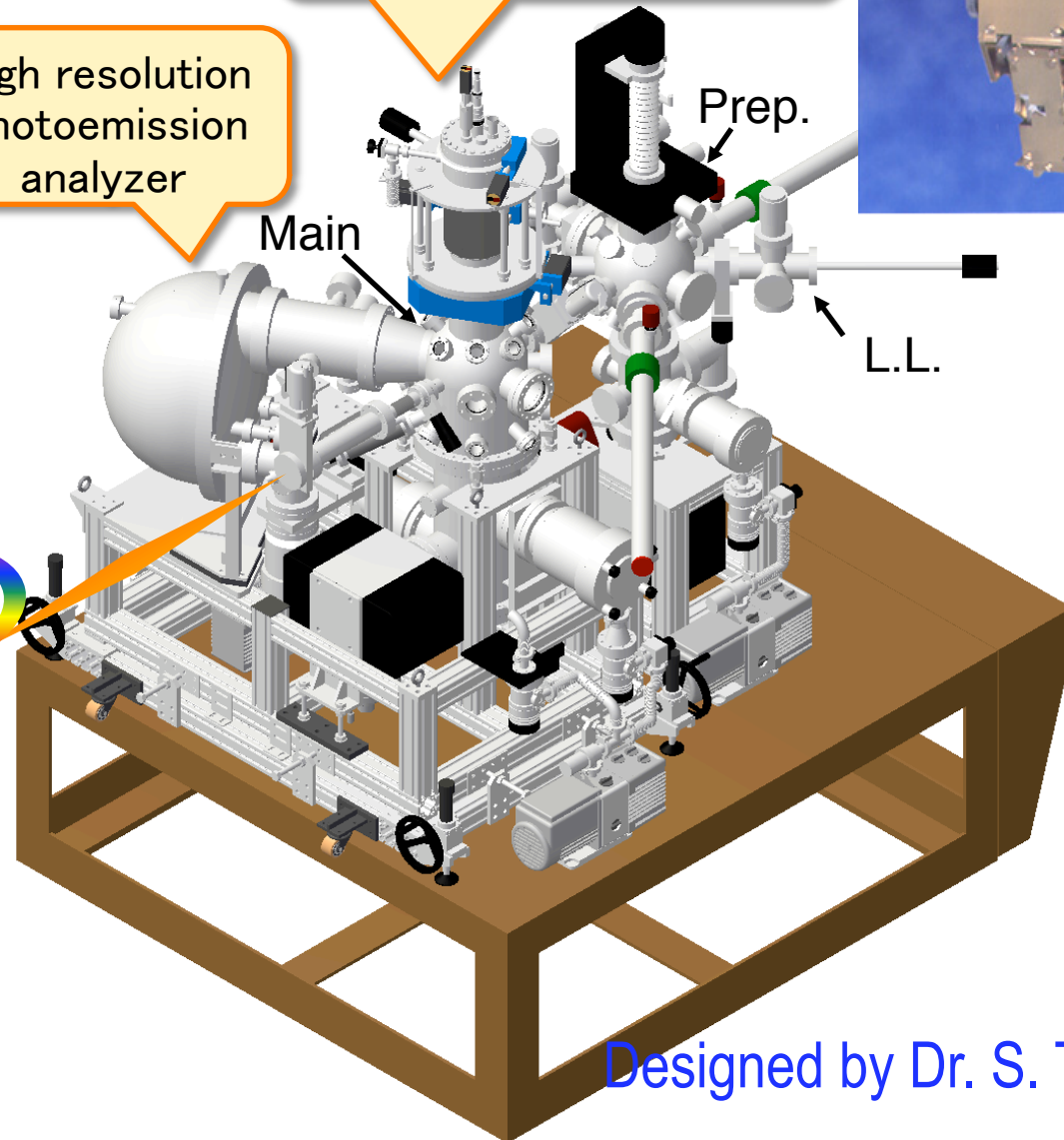
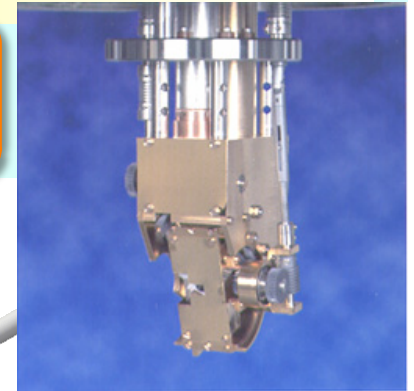
62 meV
@600 eV

Photoemission Chamber@PF BL2C



High resolution
Photoemission
analyzer

Manipulator
(Bi-axial rotating stage)

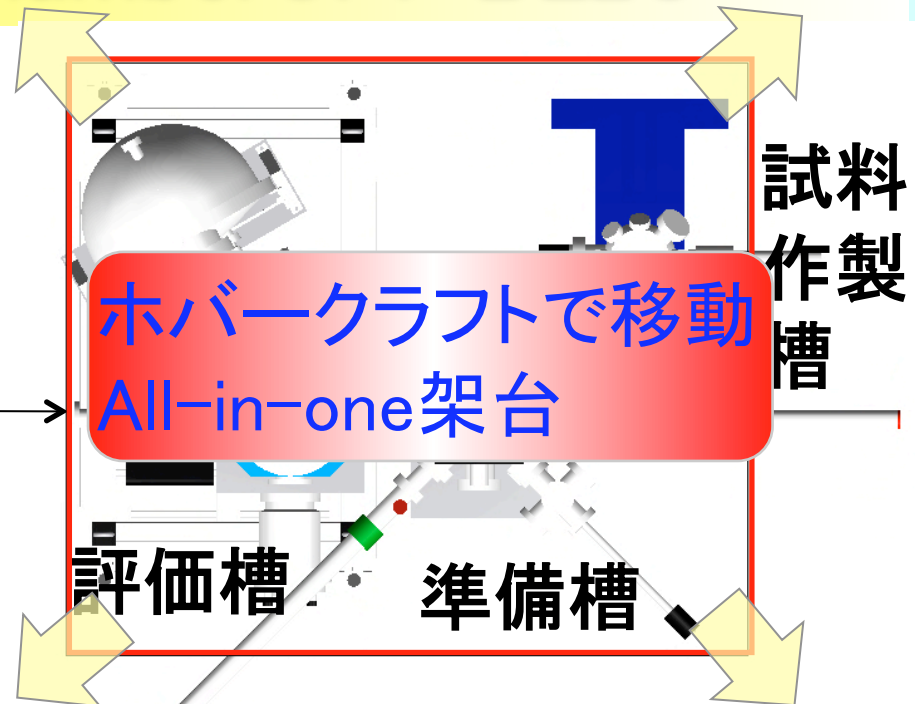
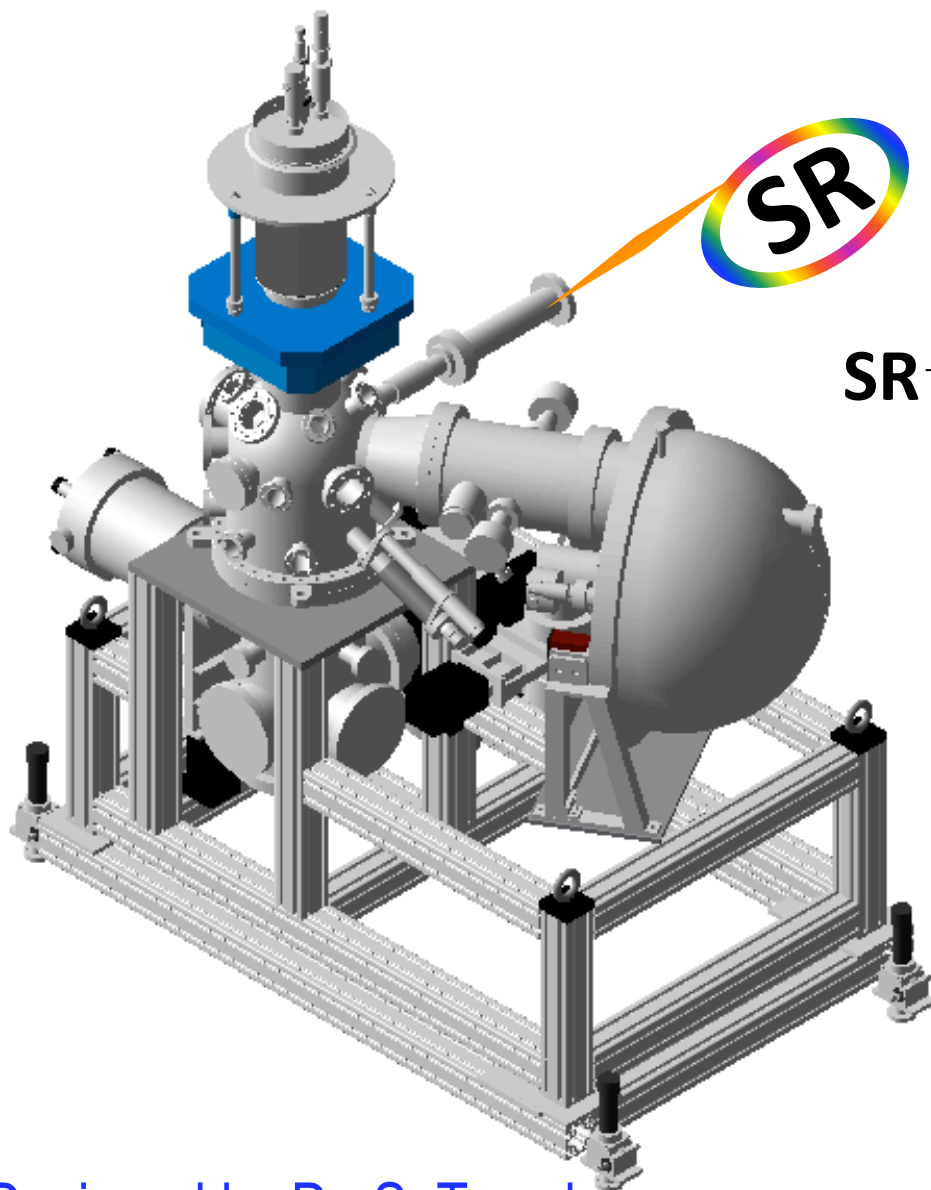


VGScienta SES2002



Designed by Dr. S. Toyoda

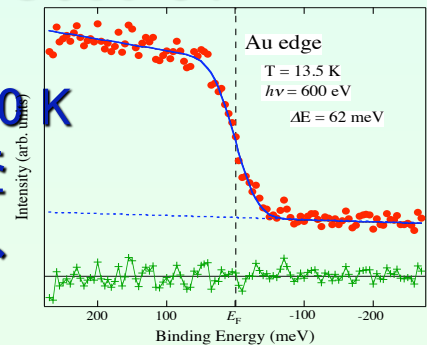
Photoemission Chamber@PF BL2C



全エネルギー分解能(光+分析器)
($E/\Delta E$) : 10,000

: 60 meV@600 eV

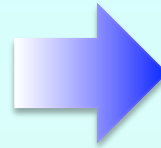
角度分解能: 0.1°
試料温度: 10 ~ 400 K
二軸試料角度走査
フェルミ面 mapping、
LD-XAS



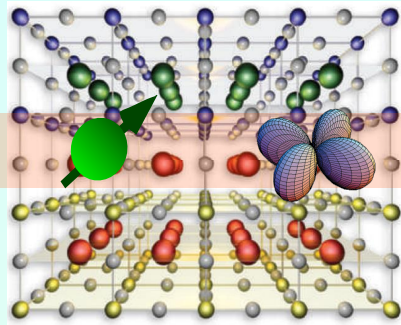
Designed by Dr. S. Toyoda

ARPES@BL2Cの研究展開

機能性遷移金属酸窒化物
(O, N, Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zn)



BL2C@PF (250-1400 eV)



強相関超構造 Physics

強相関酸化物へテロ構造による新しい量子相の研究
近年、世界的に界面が強相関系研究のフロンティアに

Chemistry

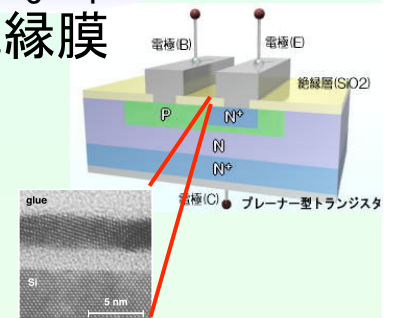
2次(Li)電池、燃料電池
省エネ・環境技術材料の評価・設計
 Li_xFePO_4 , Li_xCoPO_4 , LiCoO_2
Ptフリーカーボン触媒

ARPES@BL2C 元素選択的分光

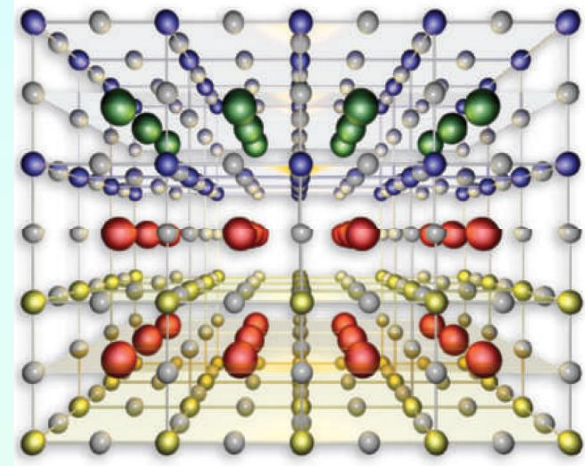
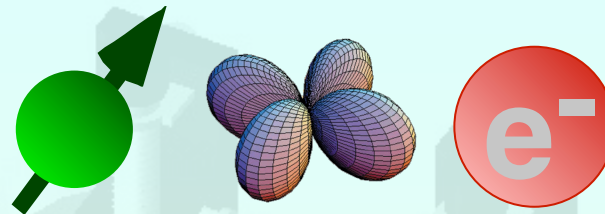
Devices

次世代不揮発性メモリ
元素戦略(レアメタルフリー)
ReRAM ($\text{Al}/\text{Fe}_3\text{O}_4$)
ULSIゲート絶縁膜

我々がパイオニアである *in-situ* ARPES+LaserMBEによる強相関酸化物へテロ構造の研究を重点的に進めると同時に、国家戦略材料の評価・設計のための産官学プラットフォームとしての場を提供する。



CONTENTS



1. Introduction

Oxide heterostructure is new frontier
in strongly correlated physics.

2. Developments of *in-situ* PES + Laser MBE system

3. *In-situ* PES on thickness-dependent SrVO_3 films

Dimensional-Crossover-Driven Metal-Insulator Transition
in SrVO_3 Ultrathin Films

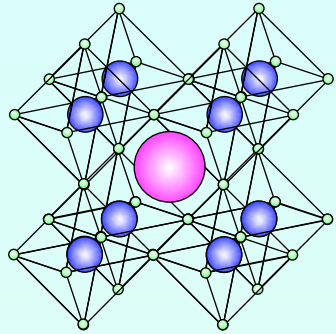
4. *In-situ* PES on LaNiO_3 ultrathin films

High-Tc Cuprate-like 2D-Fermi Surface?

5. Summary & Outlooks

Introduction

Transition Metal Oxides



High-Tc
CMR
M-I Transition

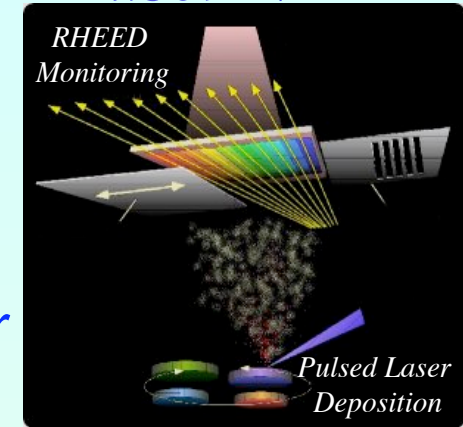
Controlling unusual
physical properties



Charge

Charge Transfer

Laser MBE



Heterostructure

Spin

Spin Exchange

Orbital

Epitaxial Strain

**Explore new functional
materials**

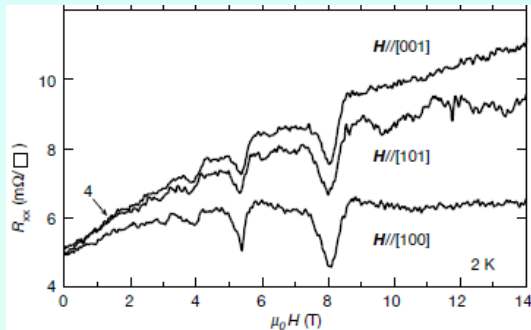


"in-situ Photoemission"

Appearance of metallic conductivity at the interface between the band insulators LaAlO_3 and SrTiO_3

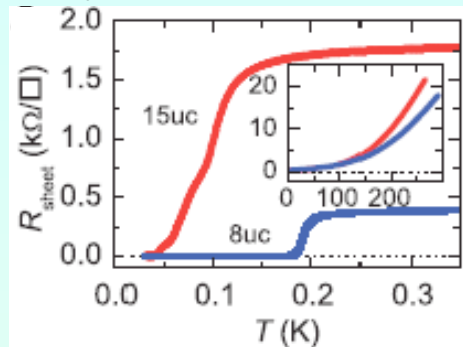
High-mobility electron gas

(A. Ohtomo *et al*, Nature 2004)



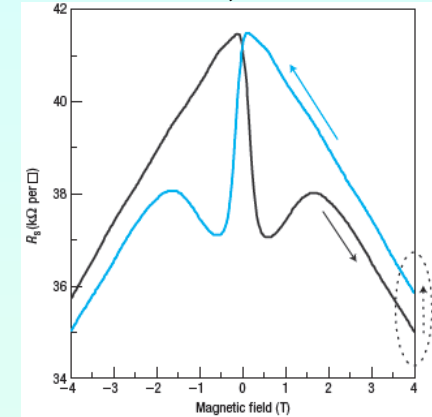
Superconductivity

(N. Reyren *et al.*, Science 2007)



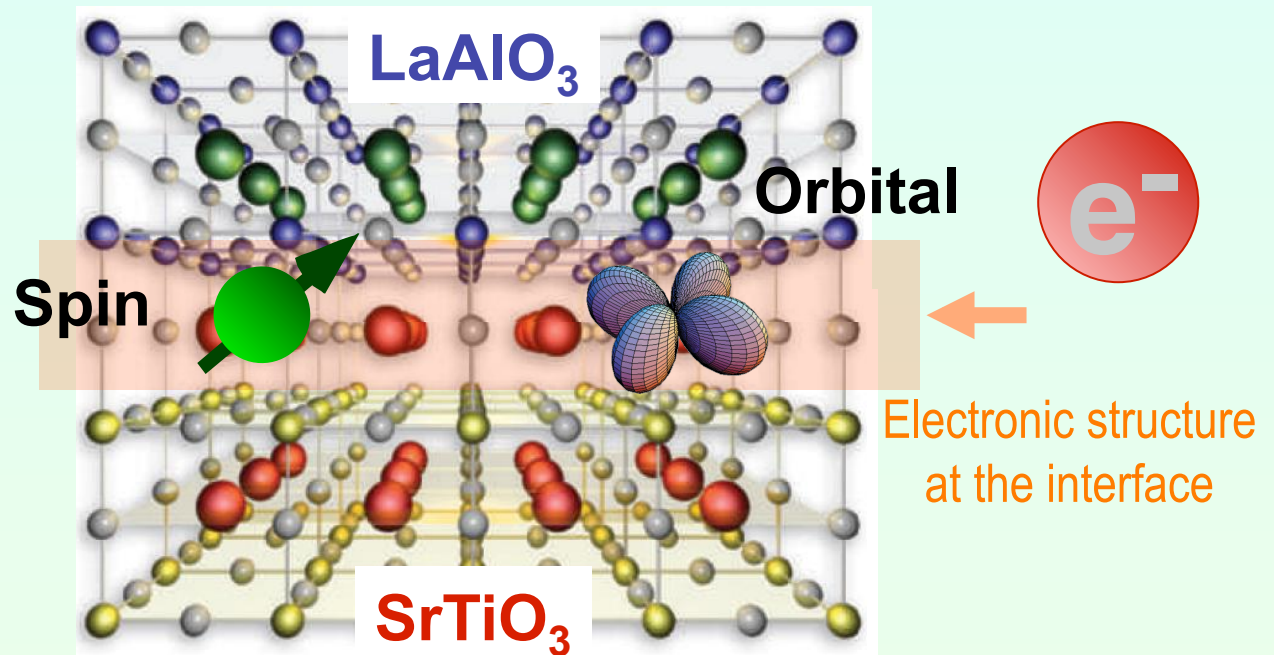
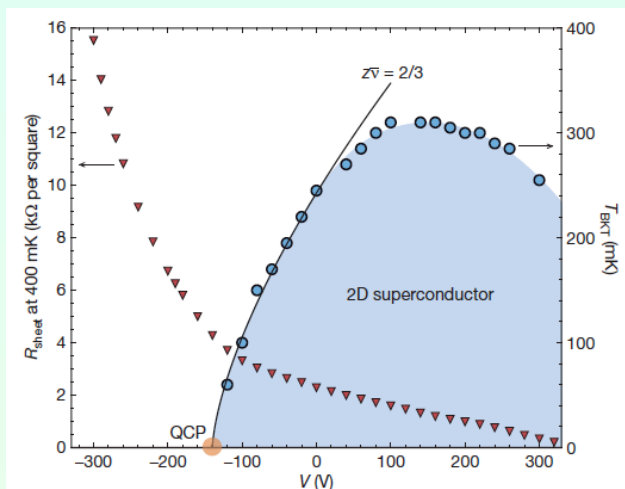
Ferromagnetism?

(A. Brinkman *et al*, Nat. Mater. 2007)



Electric field control of the superconductivity

(A.D. Caviglia *et al*, Nature 2008)

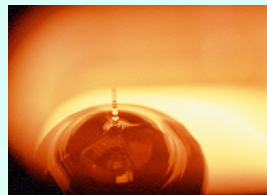


Road Map of Artificial Oxide Structures

Semiconductor (Si)

Searching materials (Bulk)

Growth of high quality
single crystal
Characterization technique
(Spectroscopy)



Understanding the semiconductor physics
(One electron picture)

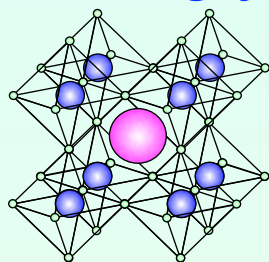
Controlling physical properties using
artificial structures



Heterostructuring

New Functionalities
(Electric devices)
New Physics
(Quantum Hall effects)

Strongly correlated oxides



Searching materials

(Bulk)

High quality single crystal
Spectroscopic technique

High-Tc

CMR

M-I Transition

Understanding the underlying physics
(Many-body effects)

Artificial structure
based on complex oxides

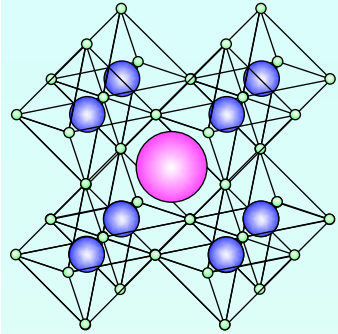
New Physics!

Controlling the anomalous
physical properties of complex oxides

Oxide heterostructures are new frontier in strongly correlated physics.

Artificial TM-Oxide Structures

Transition Metal Oxides



High-Tc
CMR
M-I Transition

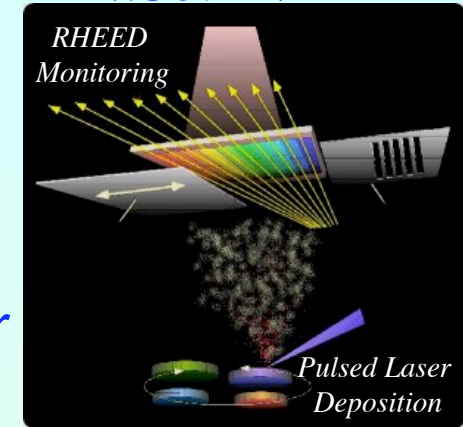
Controlling unusual
physical properties



Charge

Charge Transfer

Laser MBE



Heterostructure

Spin

Spin Exchange

Orbital

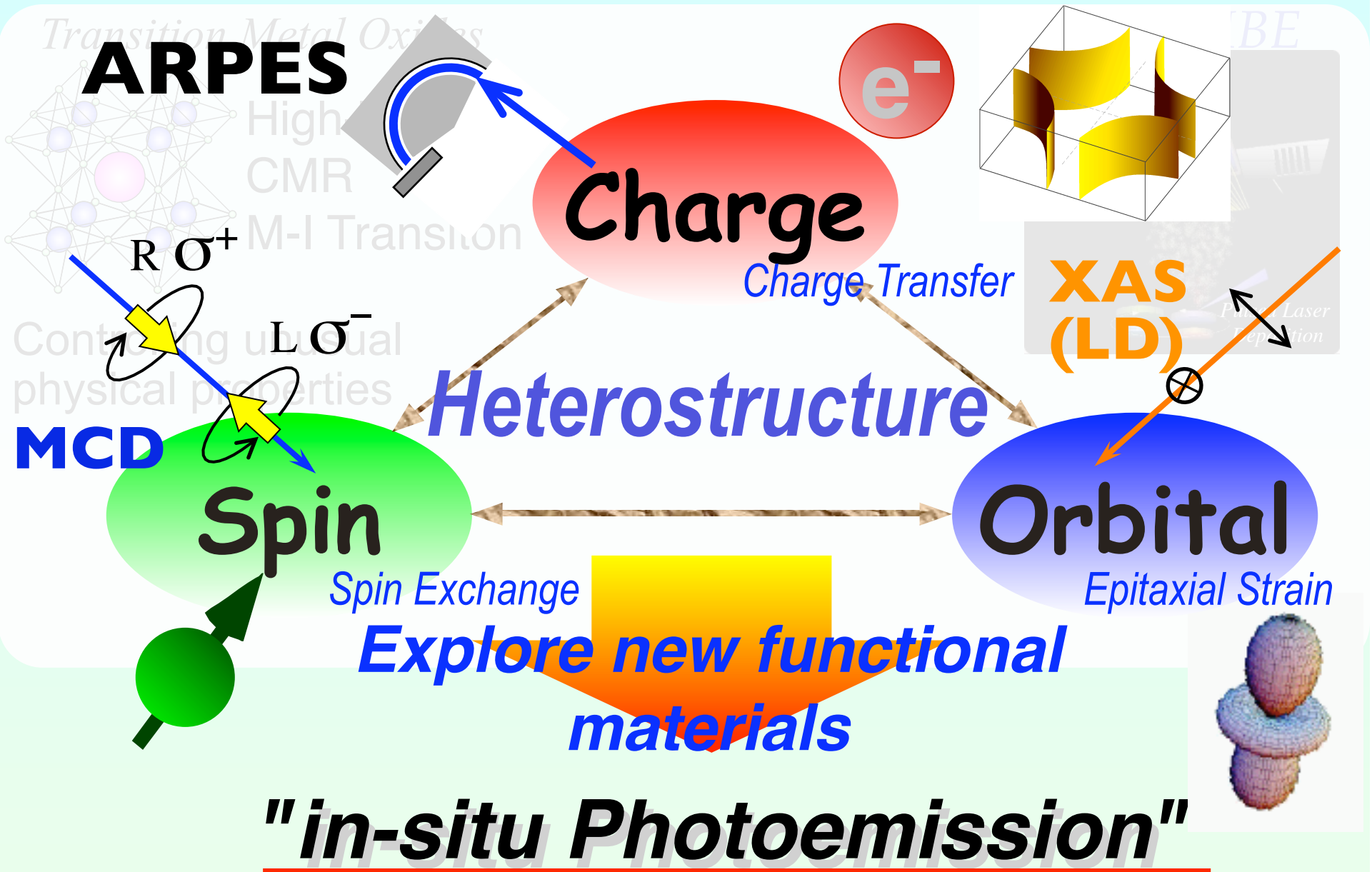
Epitaxial Strain

**Explore new functional
materials**

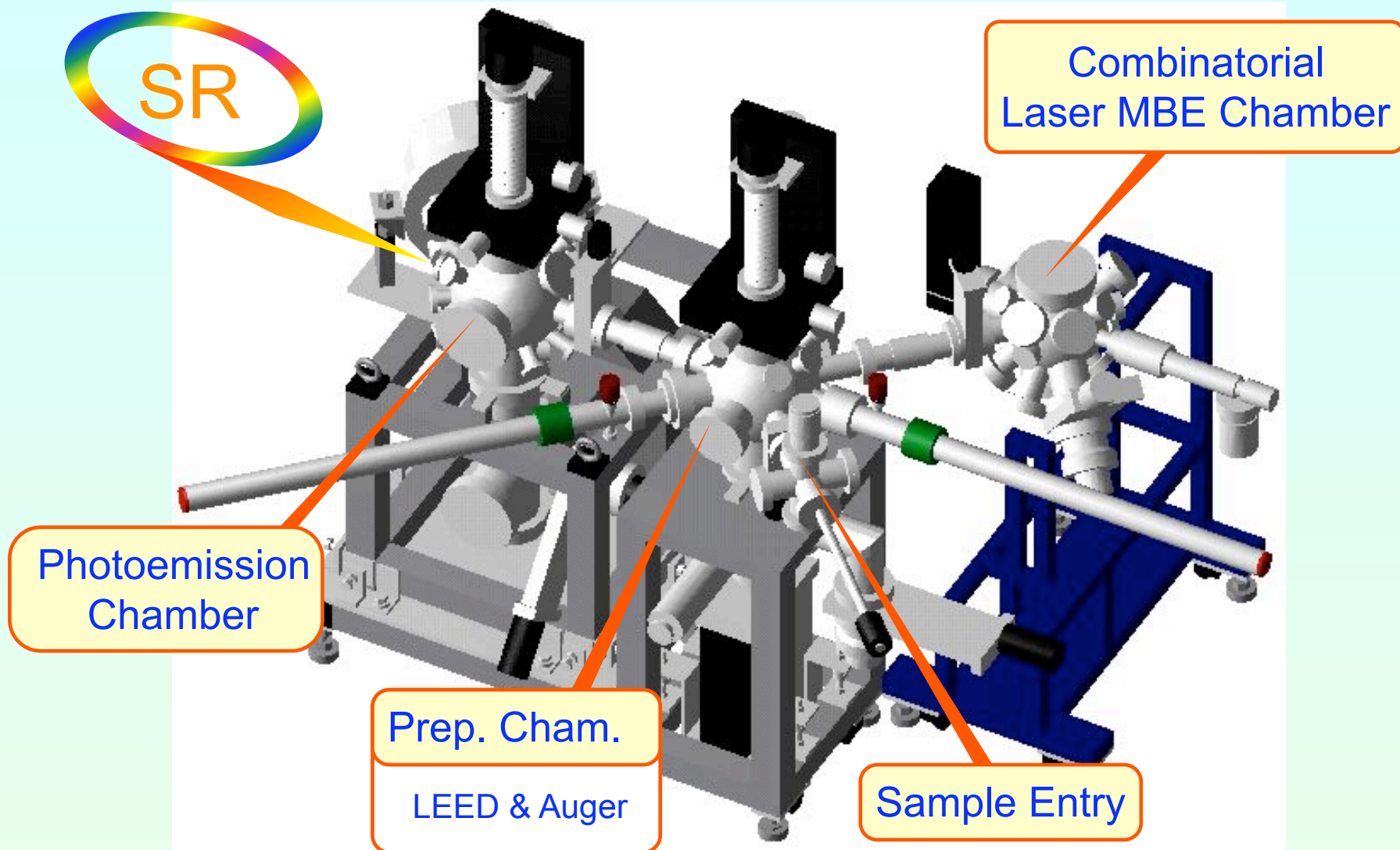


"in-situ Photoemission"

Artificial TM-Oxide Structures

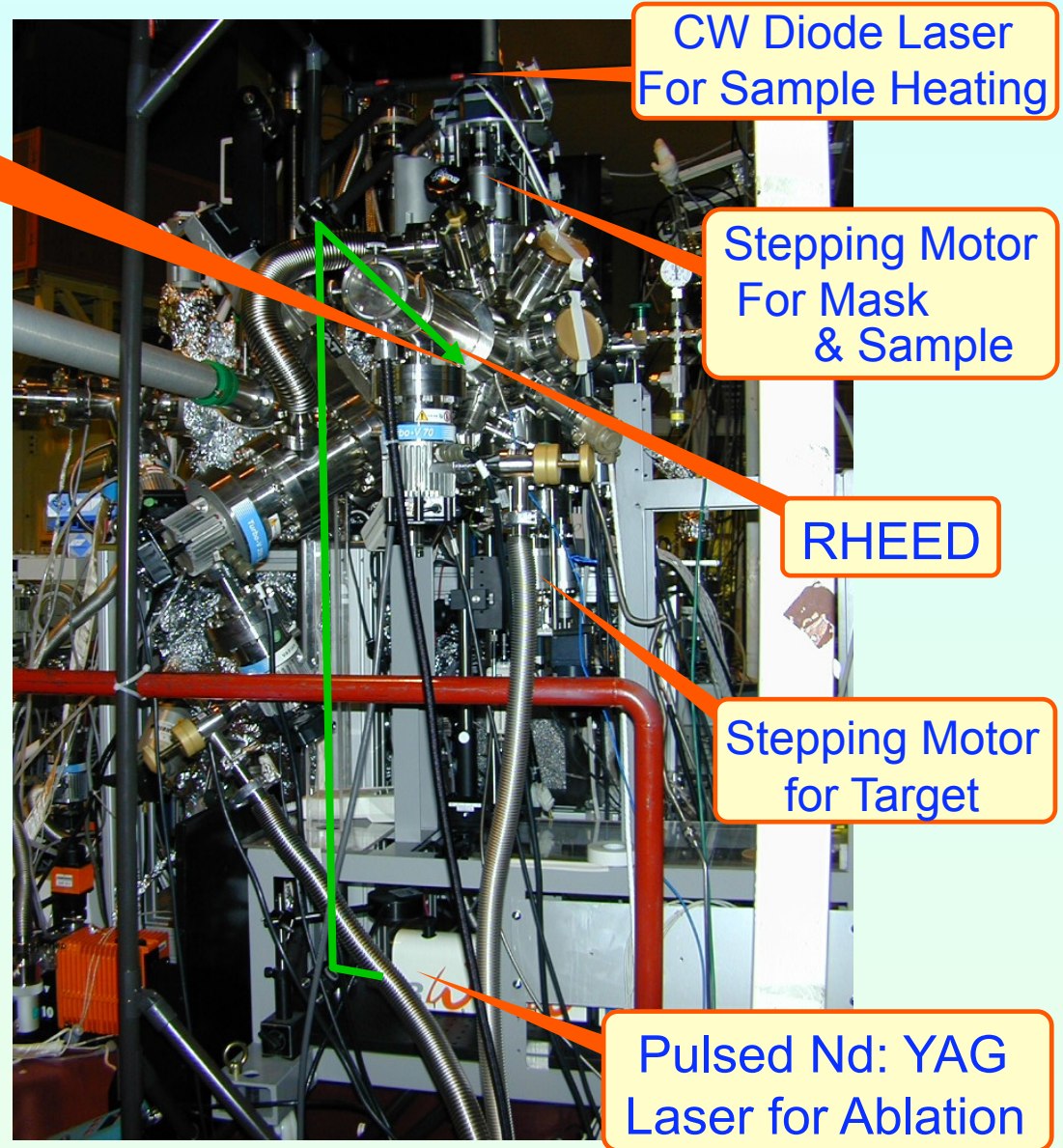
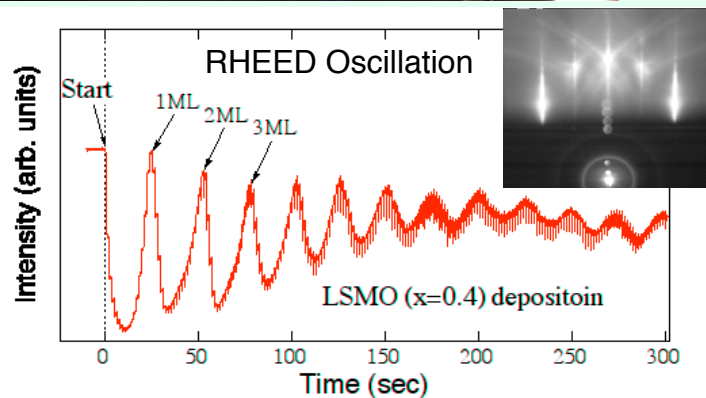
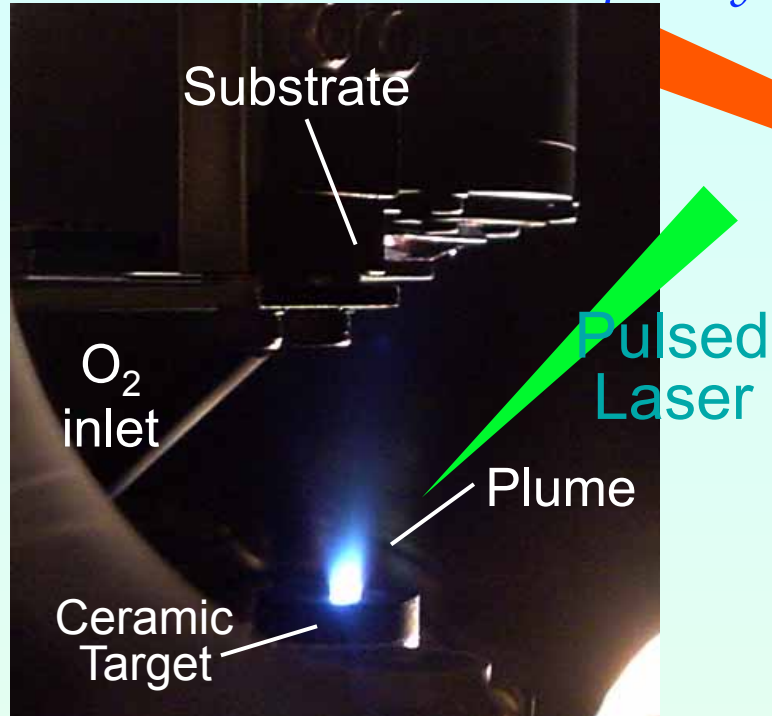


In-situ PES + Laser MBE system

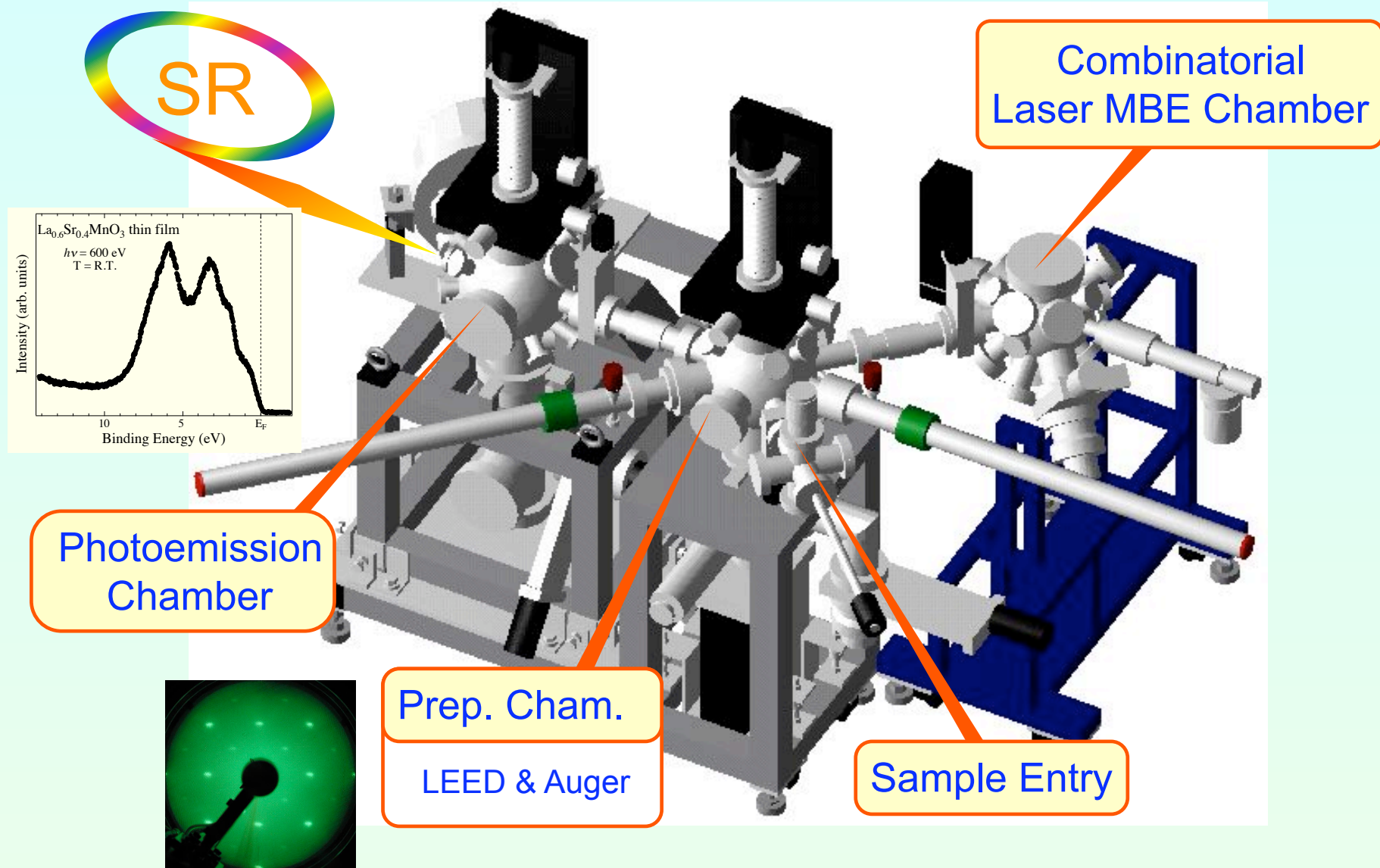


Combinatorial Laser MBE Apparatus

Laser Molecular Beam Epitaxy



In-situ PES + Laser MBE system



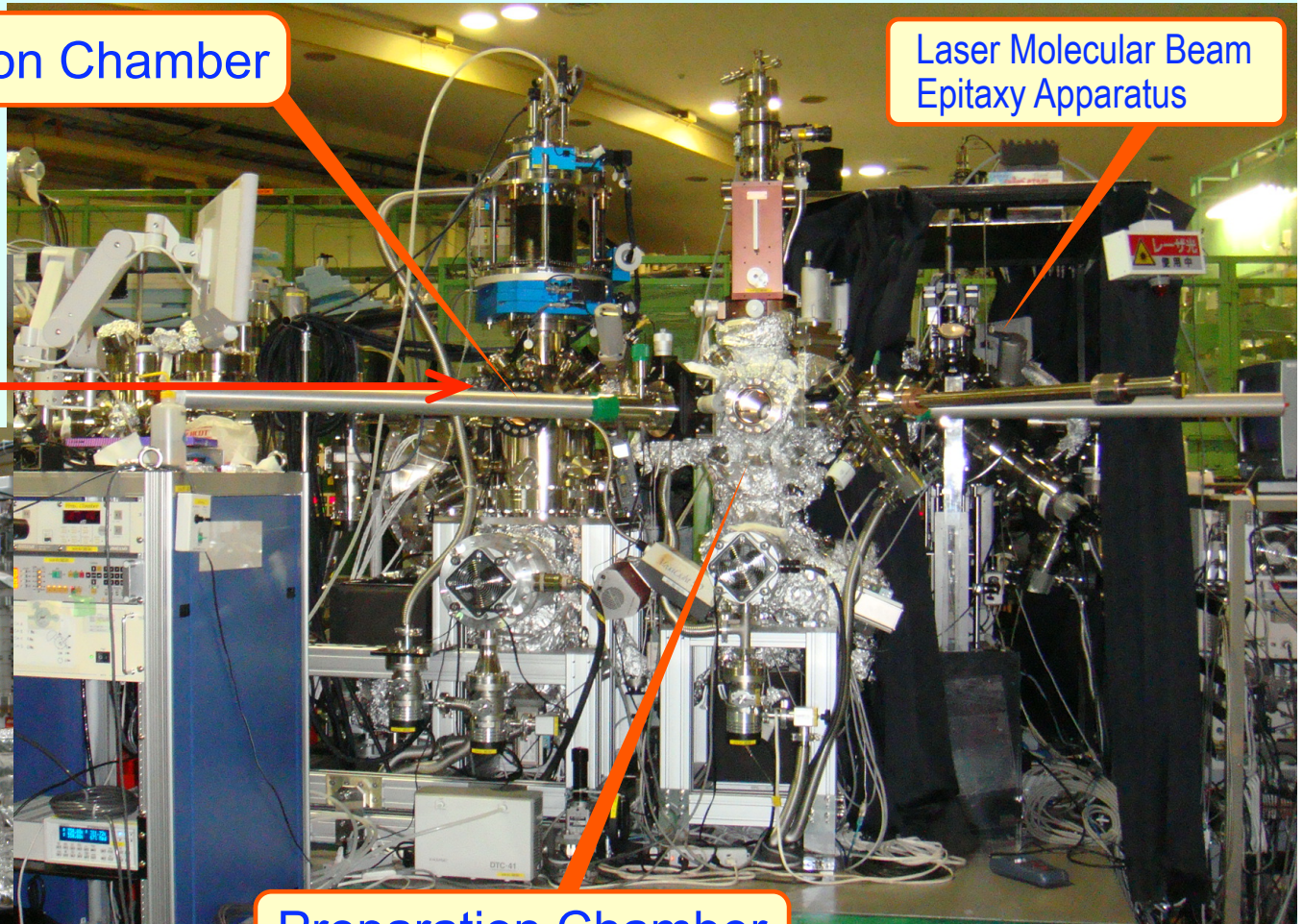
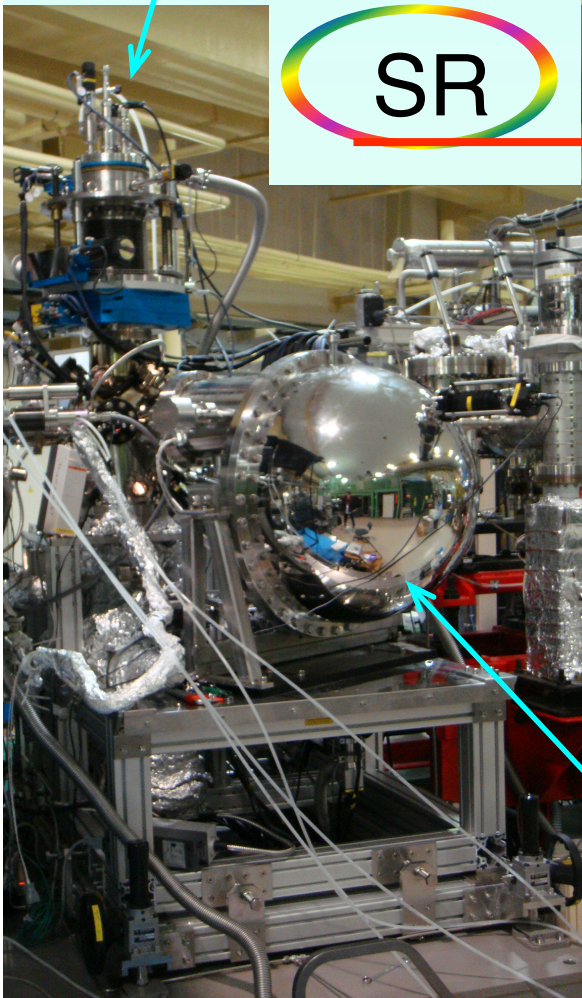


New *in-situ* PES + Laser MBE system

Photoemission Chamber

Laser Molecular Beam Epitaxy Apparatus

Manipulator
(two-axial rotating stage)



Preparation Chamber

@KEK-PF BL-2C

High resolution photoemission analyzer
VG-Scineta SES2002

In-situ Photoemission Studies on Surface and Interface of Oxide Heterostructures

REVIEW ARTICLE

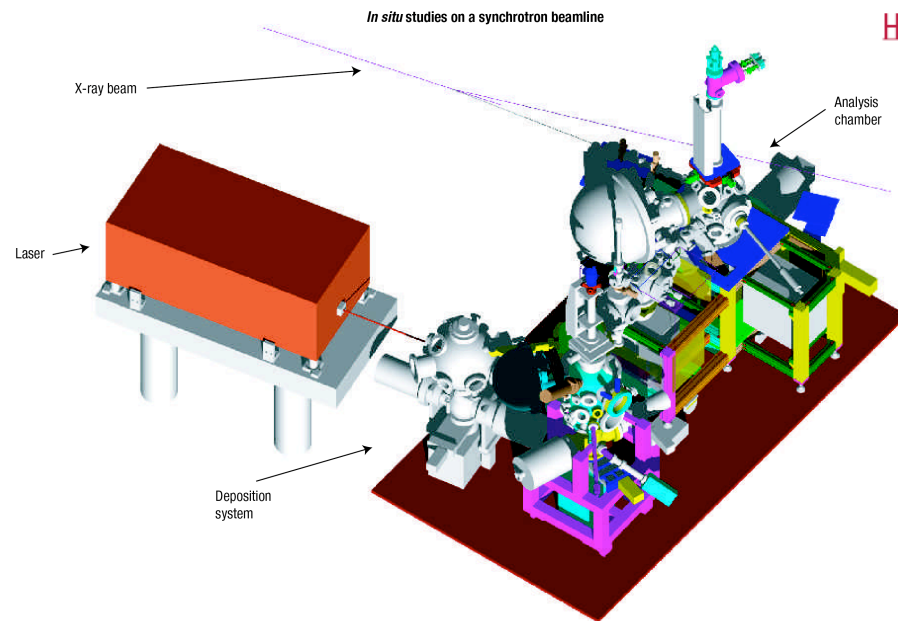
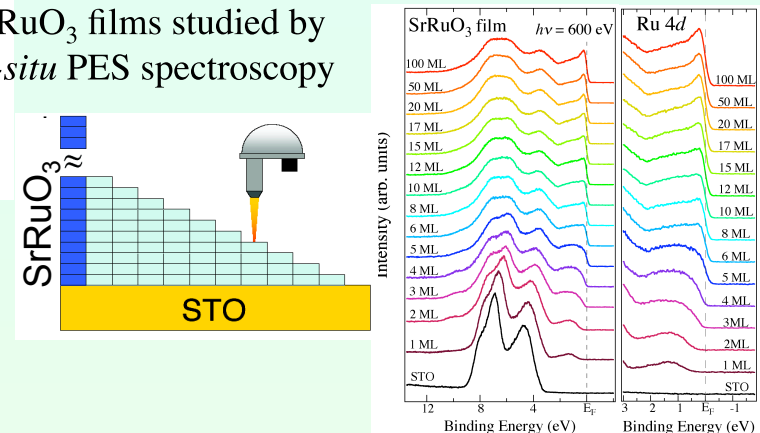


Figure 3 A schematic illustration of a thin-film deposition system (in this case a laser MBE system) that is attached to a synchrotron beamline. Such a system makes it easier to probe the electronic structure of surfaces and interfaces as the heterostructure is being grown. In the field of complex oxides, such *in situ* facilities are just emerging.

HORIZONTAL MULTILAYER HETEROSTRUCTURES

Finally, we mention that the field of horizontal heterostructure multiferroics is starting to benefit immensely from the use of a variety of surface-sensitive electronic probes such as angle-resolved photoemission (ARPES). An emerging area of research involves the probing of surface and near-surface interface electronic structure *in situ*. For this, the deposition process must be connected *in situ* to the probe; although this is common in semiconductor heteroepitaxy, it is only just evolving in complex oxide heteroepitaxy. Such systems, shown schematically in Fig. 3, are currently being designed in several laboratories around the world, and promising preliminary results are emerging⁸⁴.

Thickness dependent electronic structure of ultrathin film SrRuO₃ films studied by *in-situ* PES spectroscopy



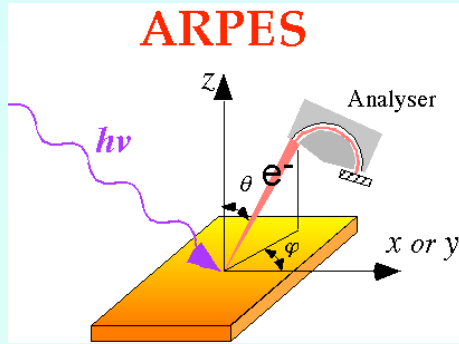
Multiferroics: progress and prospects in thin films

R. Ramesh and N.A. Spaldin, *Nature Materials* 6, 21 ('07)

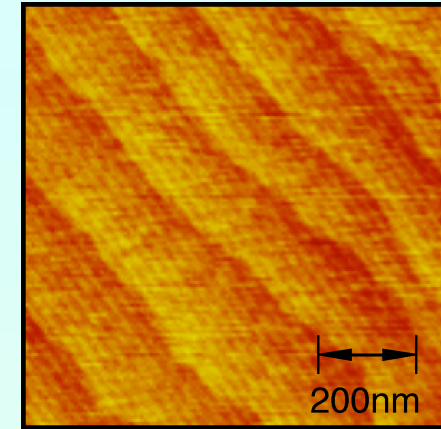
2001	2003	2005	2007	2009
PF		SPring8	ALS BESSY	SLS (Under construction)

D. Toyota *et al*, *Appl. Phys. Lett.* 87, 162508 ('05)

TM-Oxide Superstructures



Atomically flat LSMO thin film



Single crystal surface

Band Structure & Fermiology

"in-situ HR-PES"

+

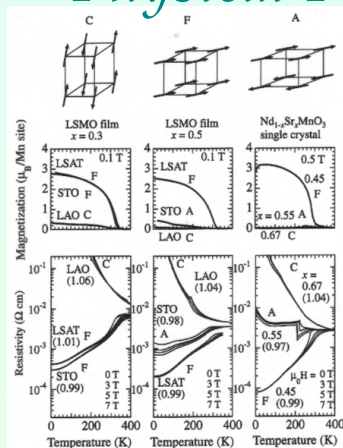
"Laser MBE"

Epitaxial Strain

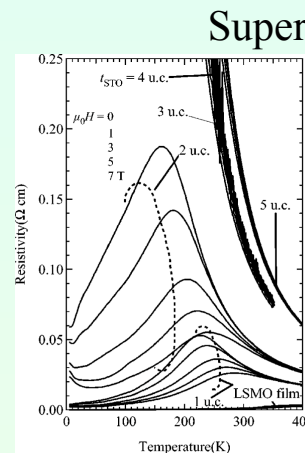
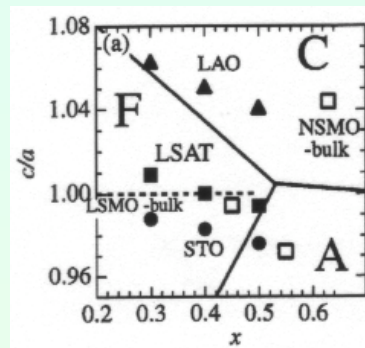
Physical Pressure

Superlattice

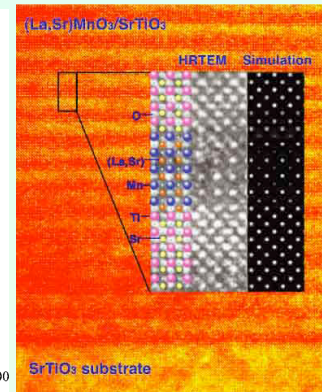
New Materials



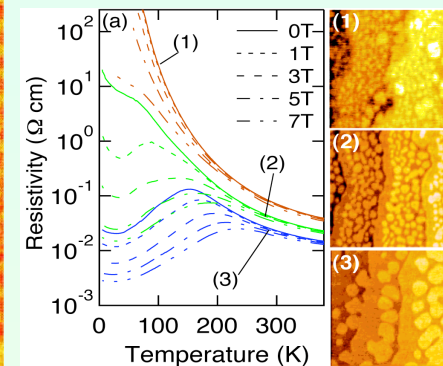
Y. Konishi *et al.*, J. Jpn. Phys. Soc. **68**, 3790 (1999).



M. Izumi *et al.*, Phys. Rev. B **64**, 064429 (2002).

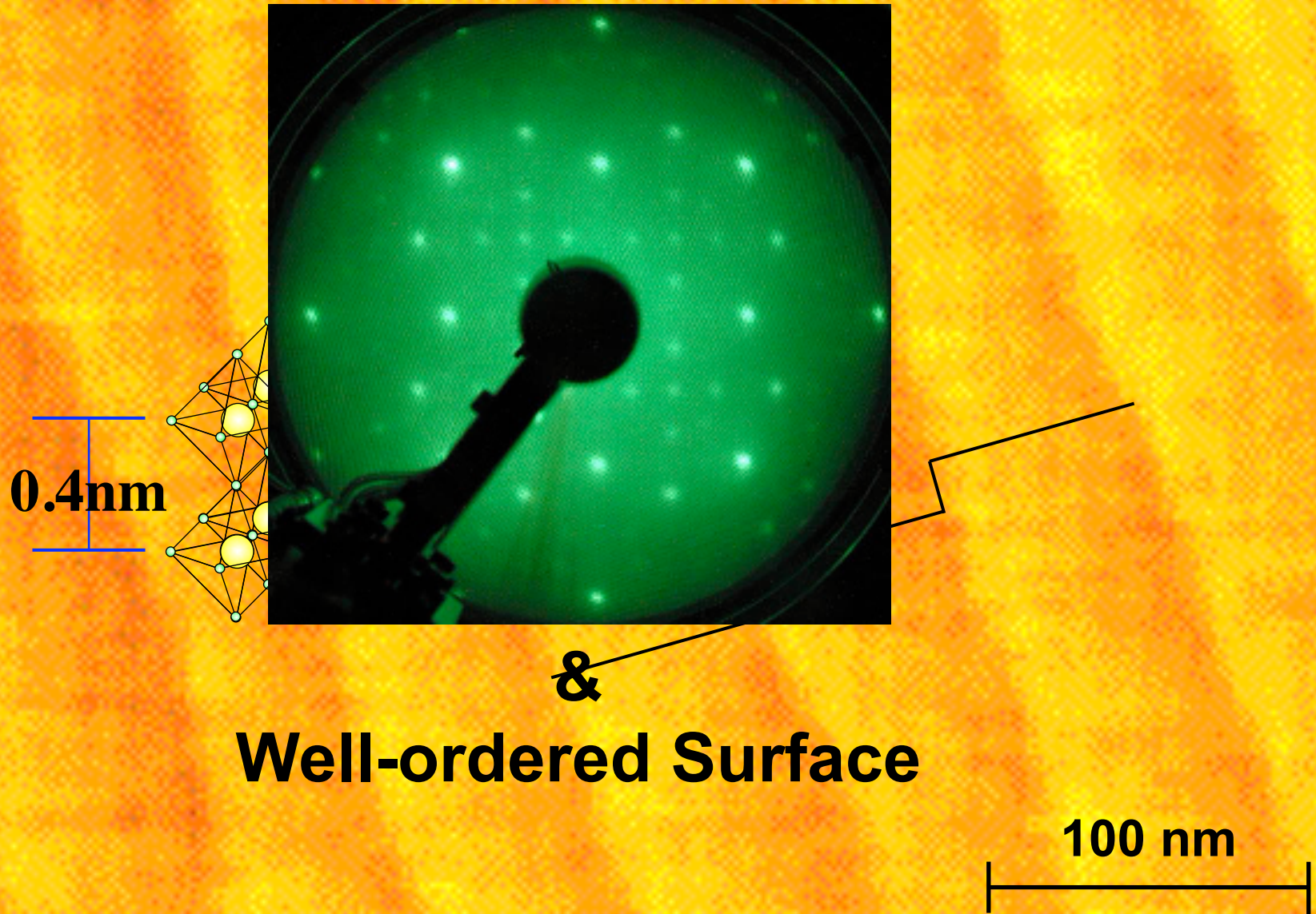


Nanodots&Nanowires

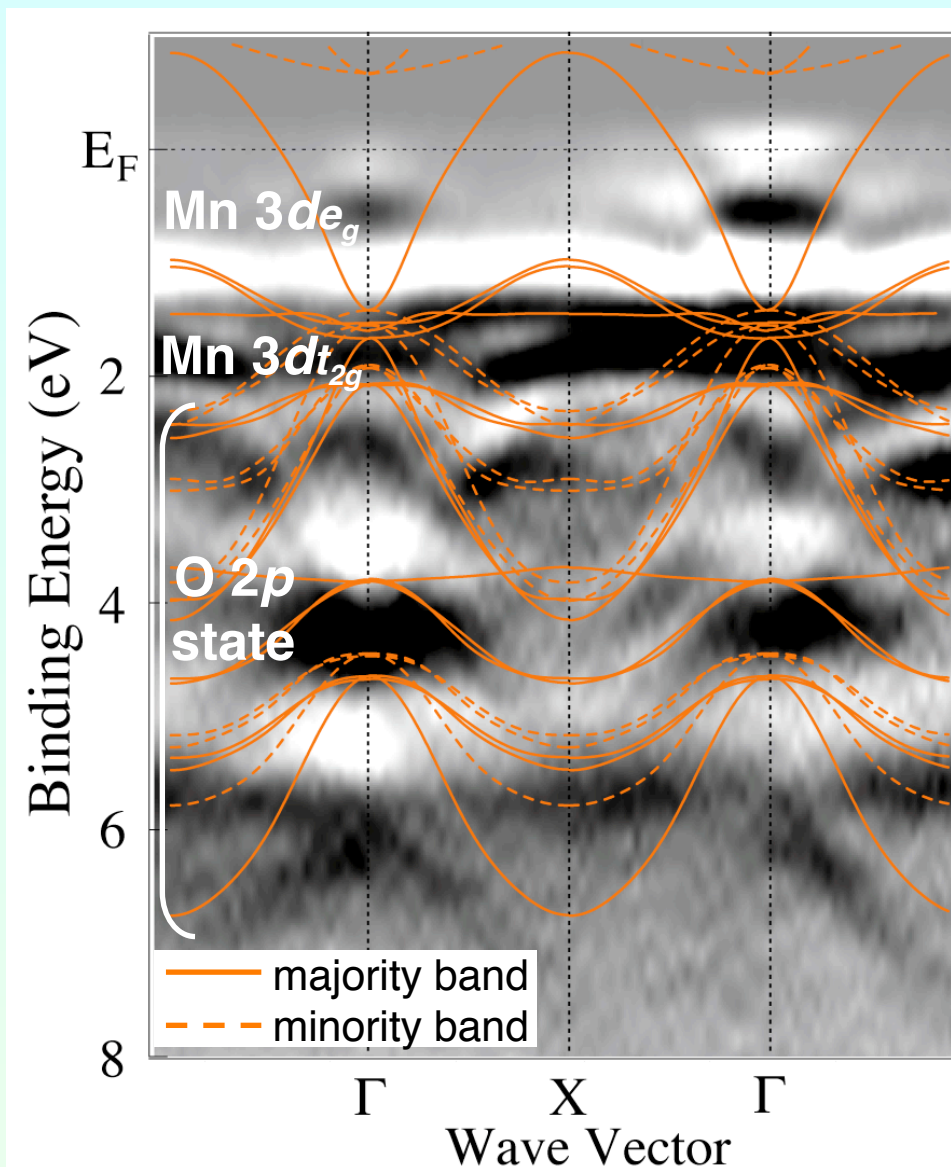
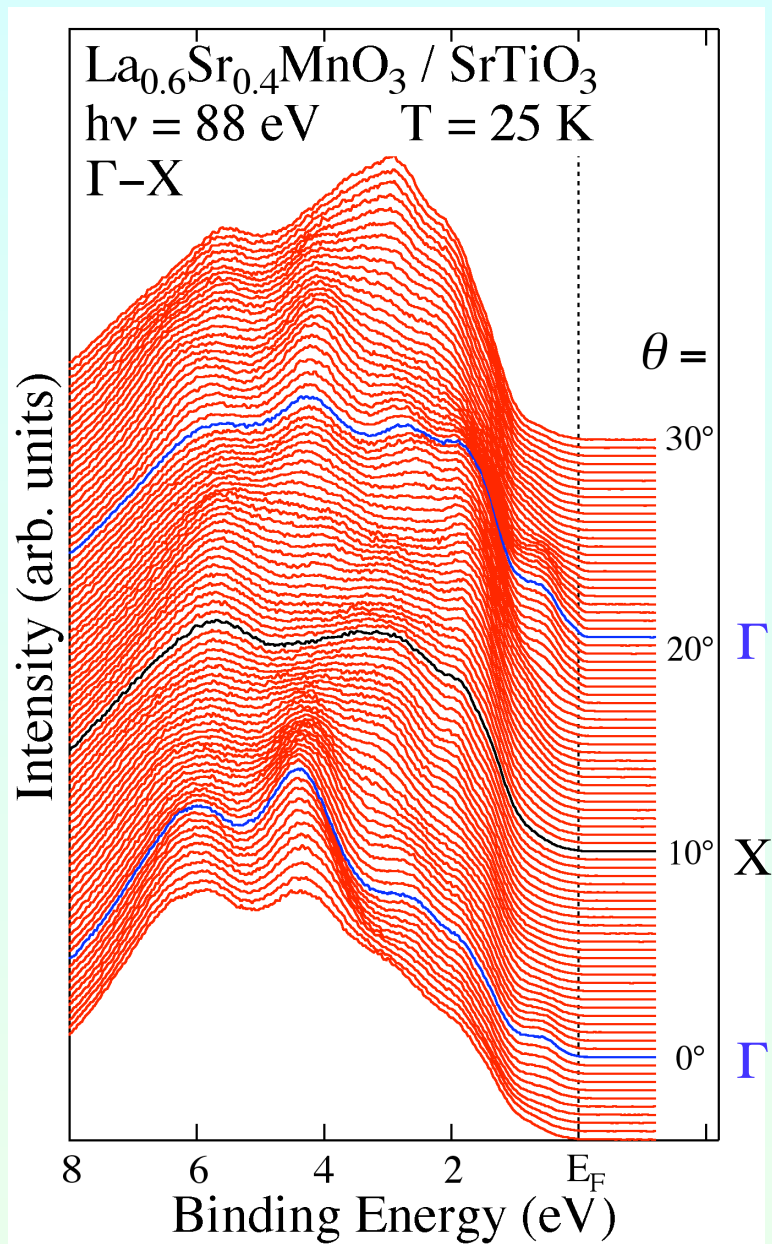


N. Nakagawa *et al.*, Jpn. J. Appl. Phys. **41**, L302 (2002)

Atomically-flat surface of $\text{La}_{1-x}\text{Sr}_x\text{MnO}_3$ thin films



Band structure of LSMO determined by *in-situ* ARPES



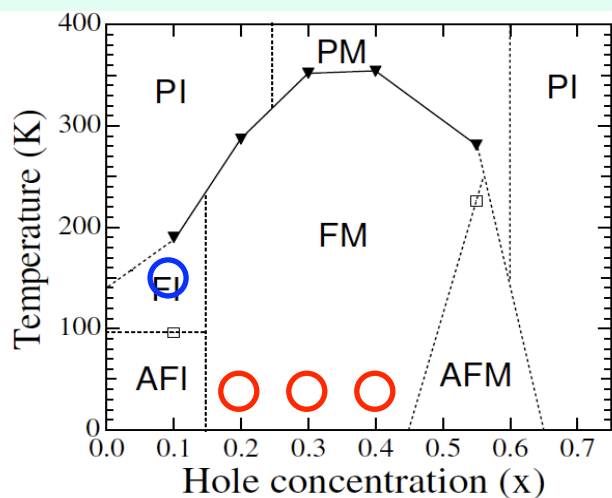
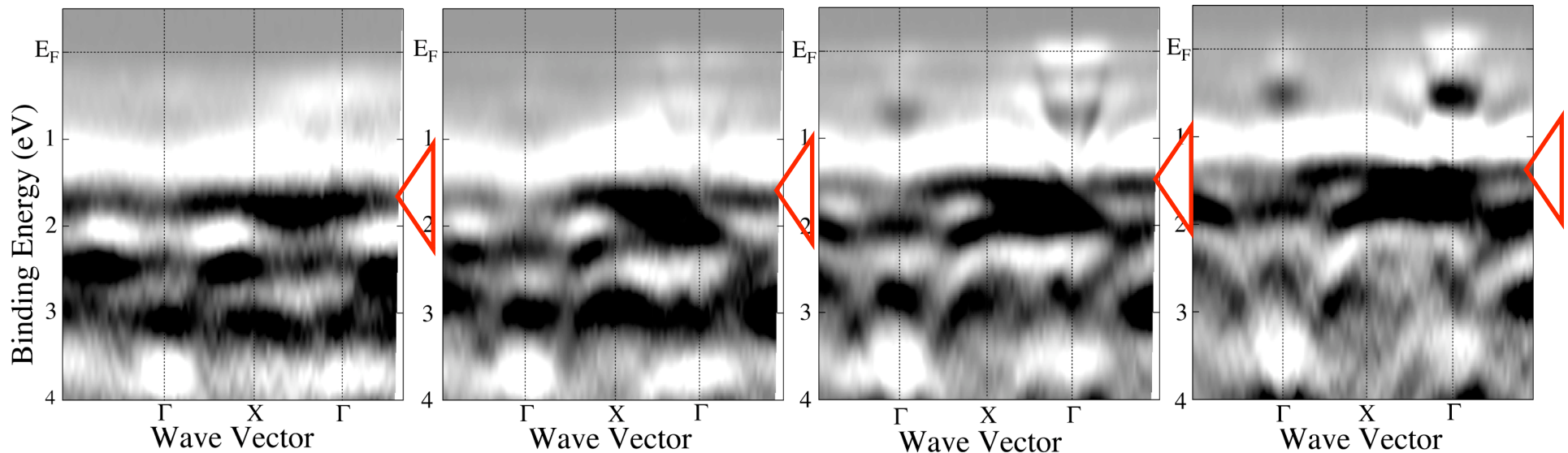
Composition dependence of Fermi surfaces

[x = 0.1]
FI

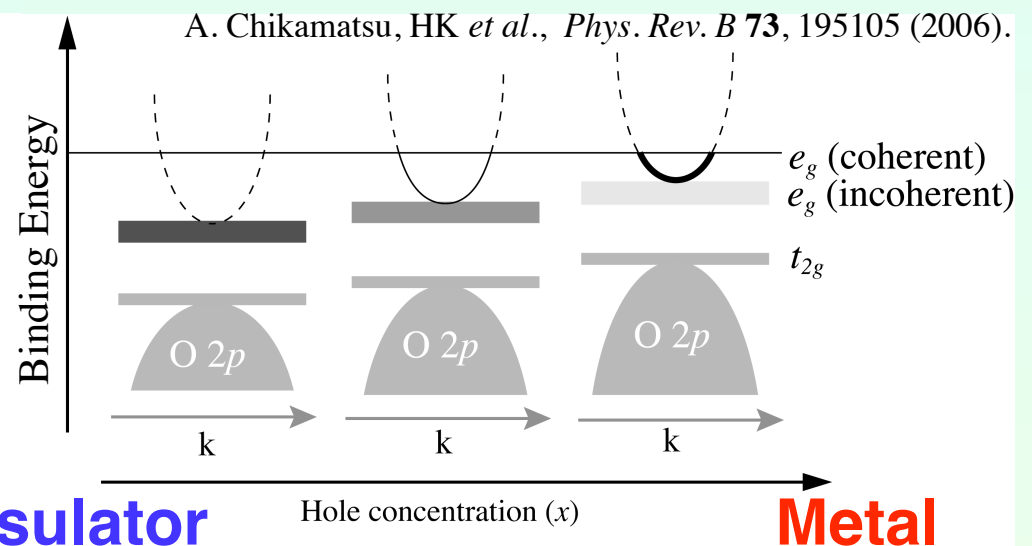
[x = 0.2]
FM

[x = 0.3]
FM

[x = 0.4]
FM



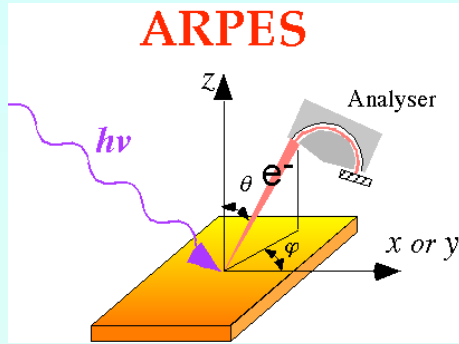
K. Horiba, HK *et al.*, *Phys. Rev. B* **71**, 155420 (2005).



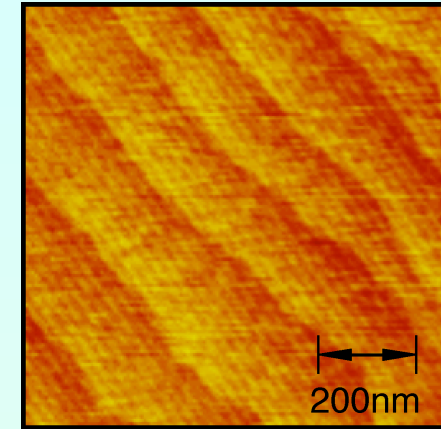
Insulator

Metal

TM-Oxide Superstructures



Atomically flat LSMO thin film



Single crystal surface

Band Structure & Fermiology

"in-situ HR-PES"

+

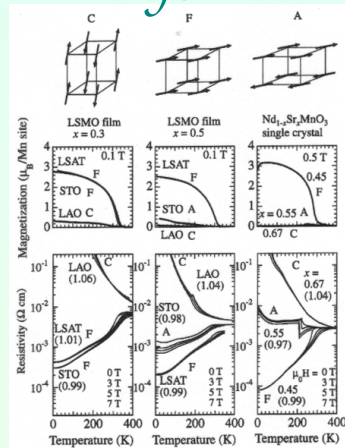
"Laser MBE"

Epitaxial Strain

Physical Pressure

Superlattice

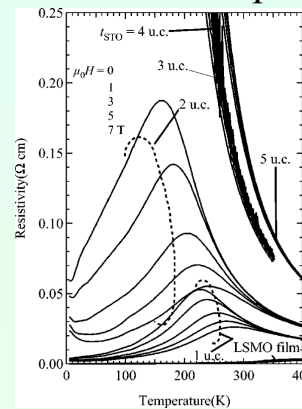
New Materials



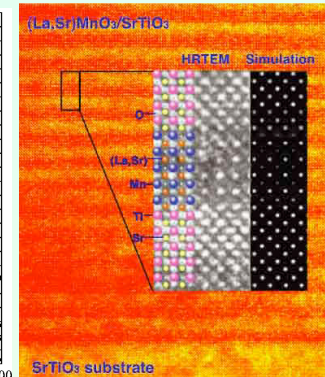
Y. Konishi *et al.*, J. Jpn. Phys. Soc. **68**, 3790 (1999).

"Laser MBE"

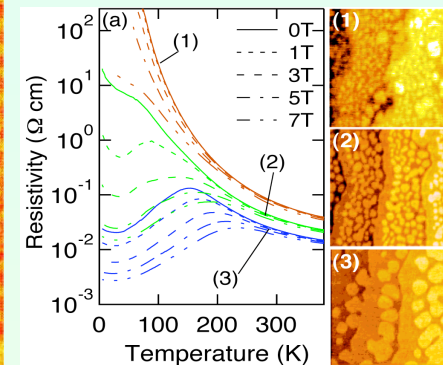
Superlattice



M. Izumi *et al.*, Phys. Rev. B **64**, 064429 (2002).



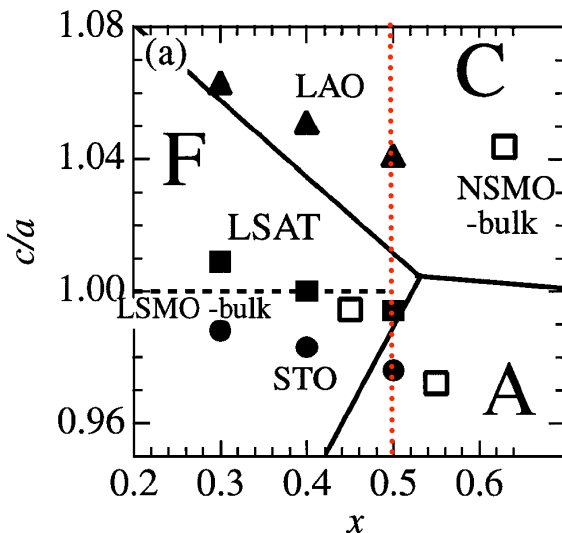
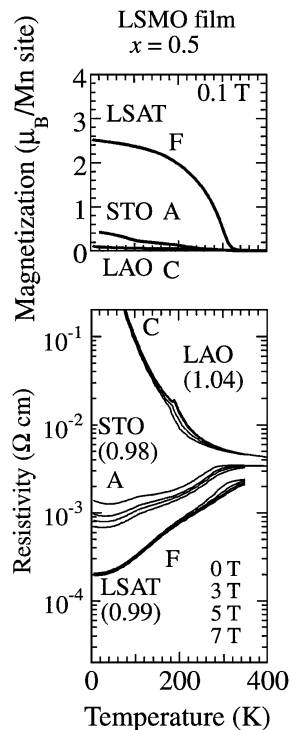
Nanodots&Nanowires



N. Nakagawa *et al.*, Jpn. J. Appl. Phys. **41**, L302 (2002)

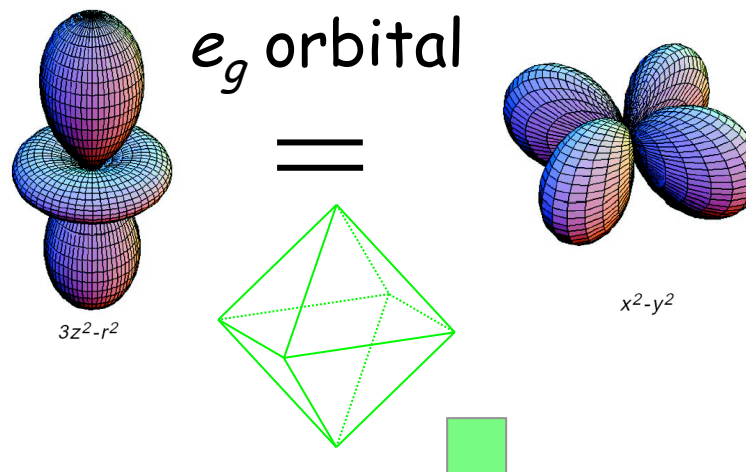
Physical Pressure Induced by Epitaxial Strain

Strain-controlled LSMO films



Y. Konishi *et al.*, J. Phys. Soc. Jpn. 68, 3790 (1999).

LSMO $x = 0.5$
LSMO/LSAT (FM)

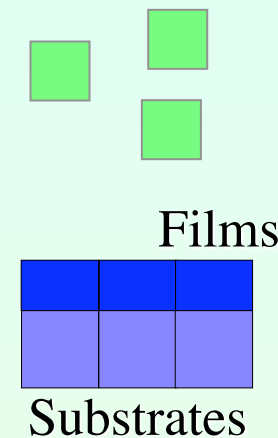
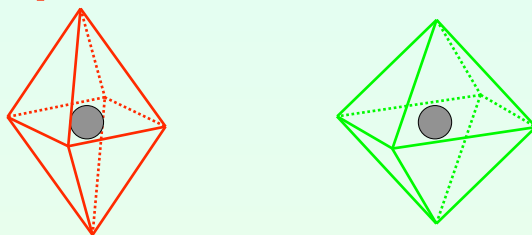
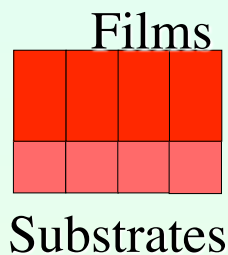


LSMO/LAO
(c-type AFI)

LSMO/STO
(A-type AFM)

Compressive

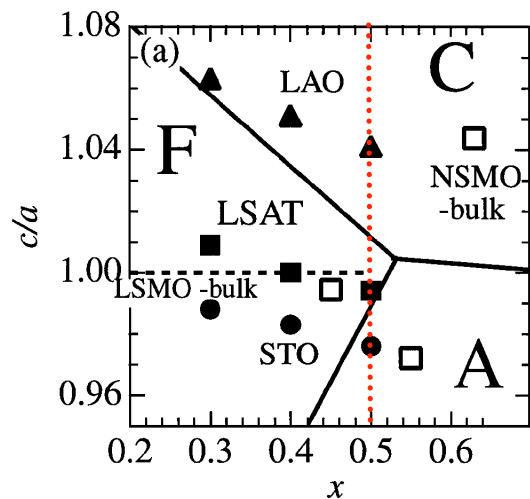
Tensile



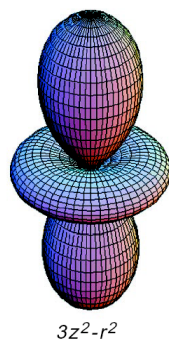
Change in electronic structure under physical pressure

Phase Controlled LSMO films by Epitaxial Strain

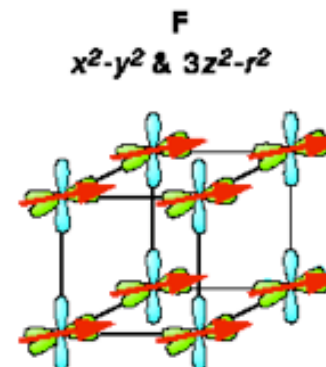
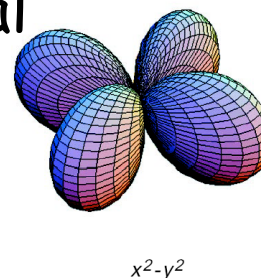
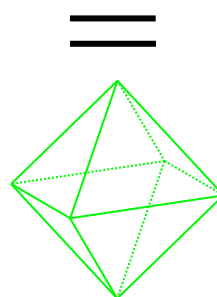
Strain-controlled LSMO films



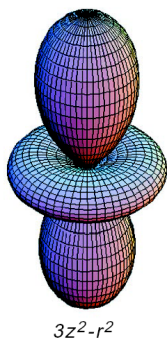
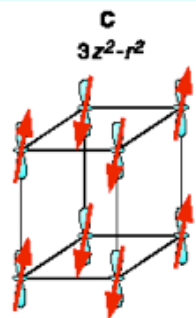
LSMO/LSAT (FM)



e_g orbital

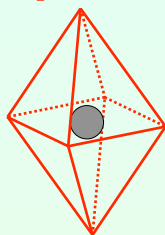


Y. Konishi *et al.*, J. Phys. Soc. Jpn. 68, 3790 (1999).



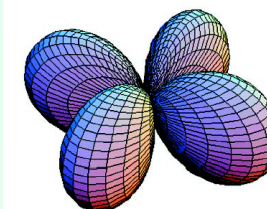
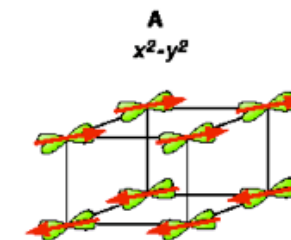
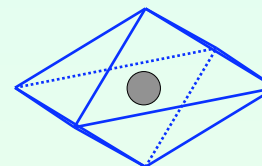
LSMO/LAO
(c-type AFI)

Compressive



LSMO/STO
(A-type AFM)

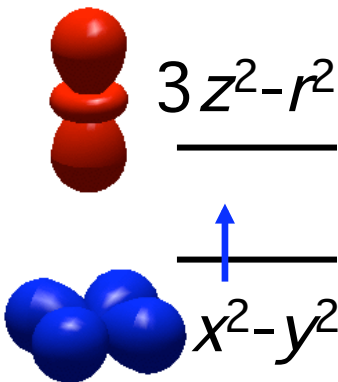
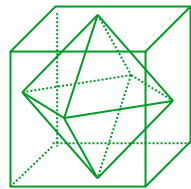
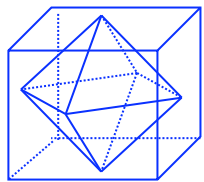
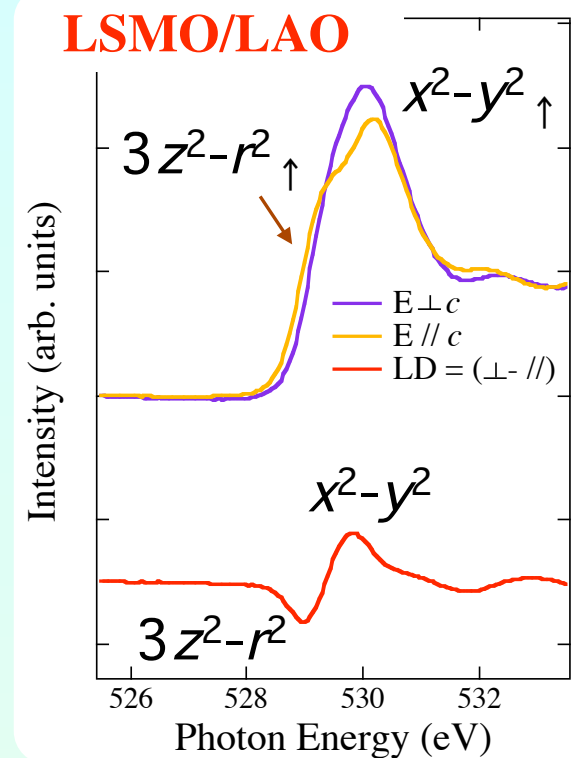
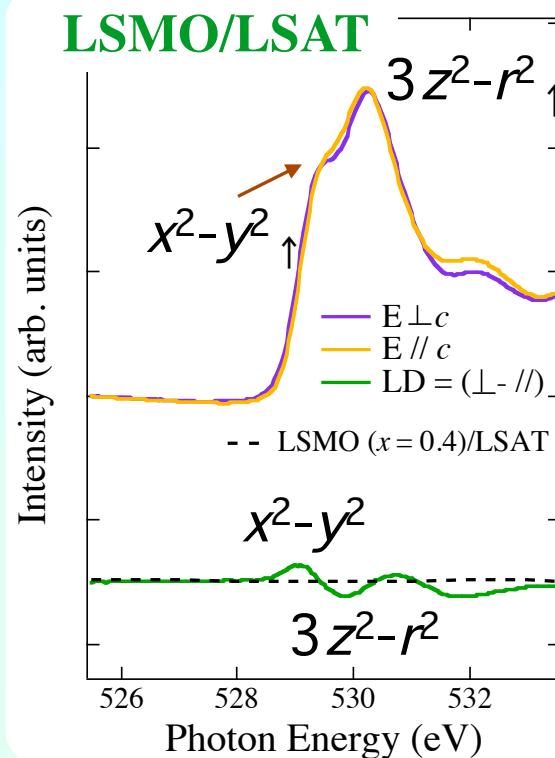
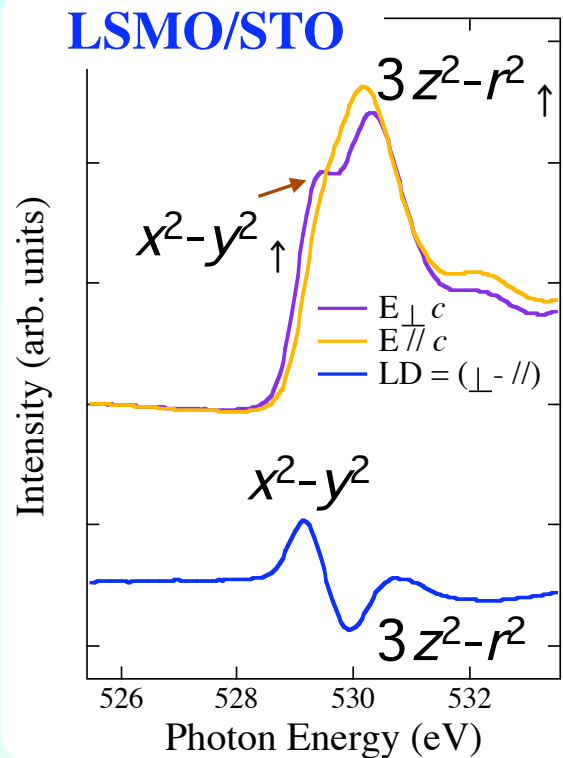
Tensile



x^2-y^2

Photoemission Studies on Phase-Controlled LSMO Films

Linear Dichroism of XAS spectra



LSMO/STO
Tensile
1.1 %

LSMO/LSAT
Tensile (week)
0.3 %



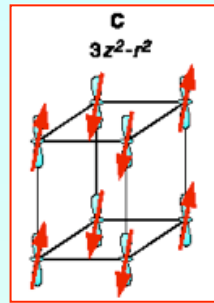
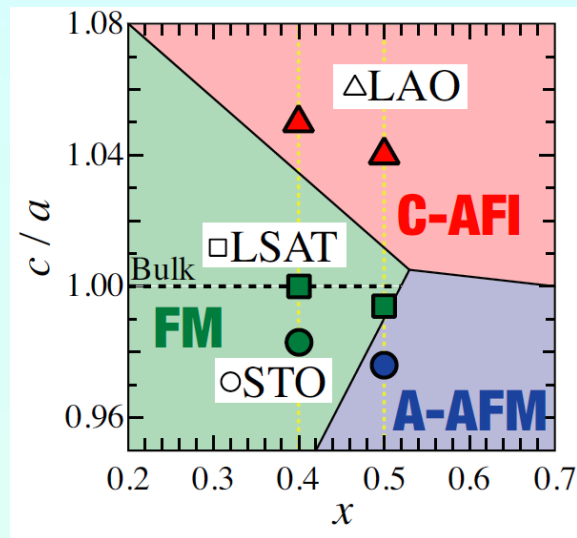
x^2-y^2

LSMO/LAO
Compressive
1.8 %



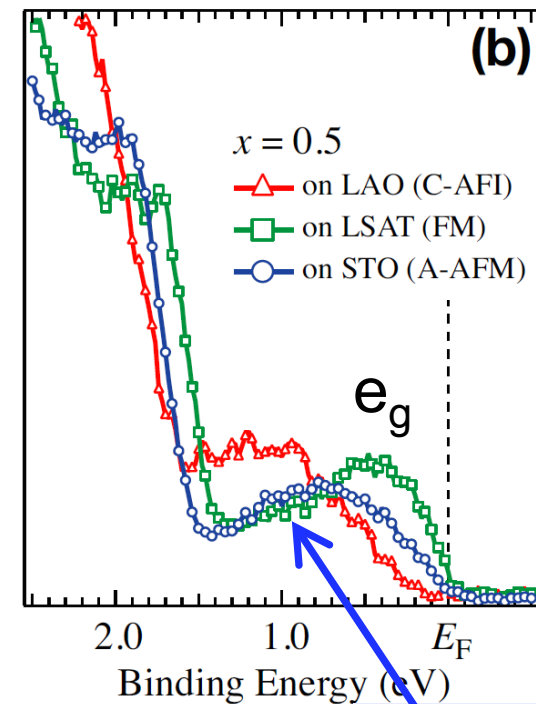
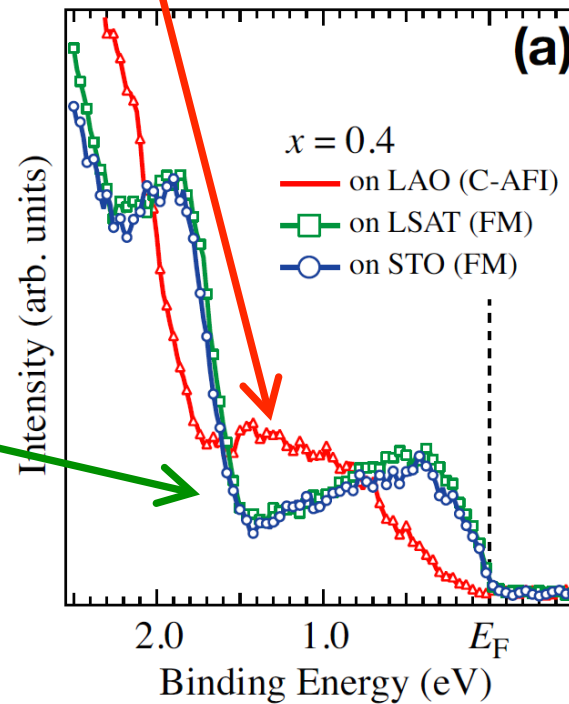
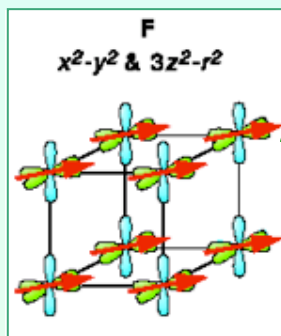
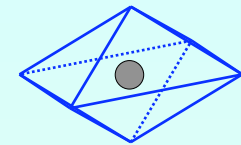
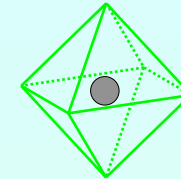
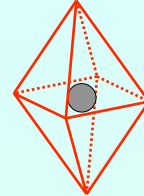
↑
 $3z^2-r^2$

HXPES Spectra of Strain-controlled LSMO



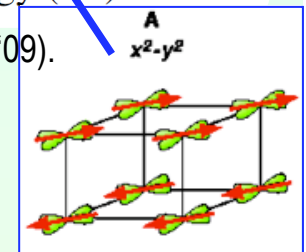
Compressive

Tensile

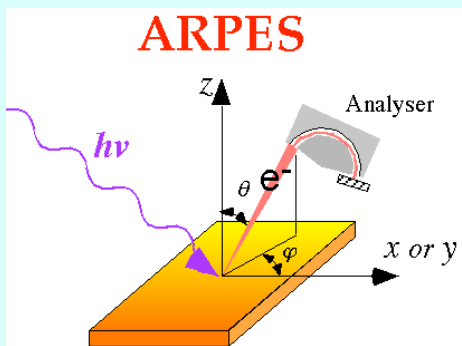


K. Horiba, HK *et al.*, Phys. Rev. B **80**, 132406 ('09).

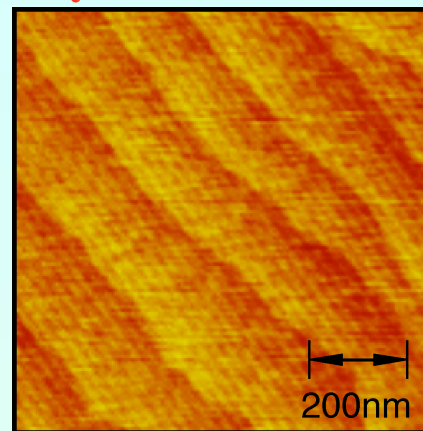
Energy Gap opens at E_F Associated with Pressure-Induced Metal-Insulator transition



TM-Oxide Superstructure



Atomically flat LSMO thin film



Single crystal surface

Band Structure & Fermiology

"in-situ HR-PES"

+

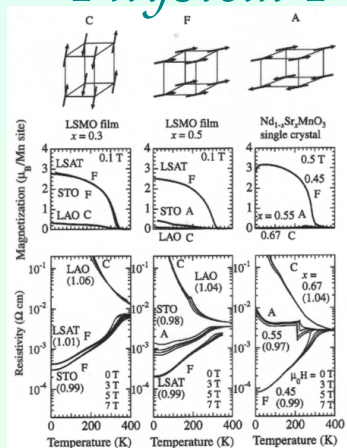
"Laser MBE"

Epitaxial Strain

Physical Pressure

Superlattice

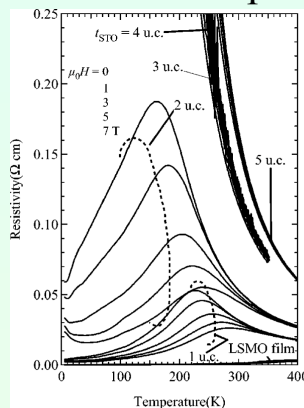
New Materials



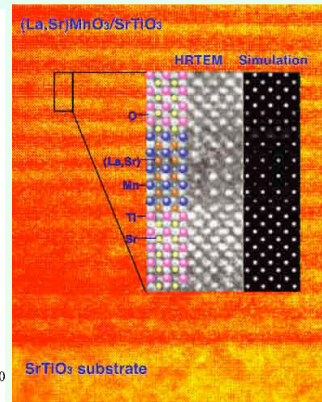
Y. Konishi *et al.*, J. Jpn. Phys. Soc. **68**, 3790 (1999).

"Laser MBE"

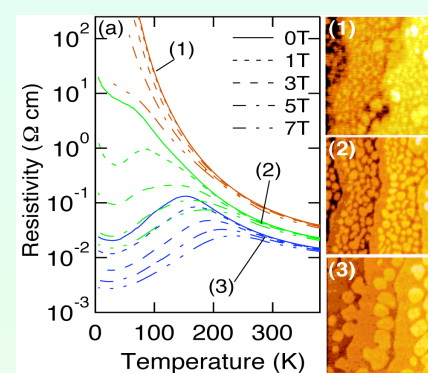
Superlattice



M. Izumi *et al.*, Phys. Rev. B **64**, 064429 (2002).



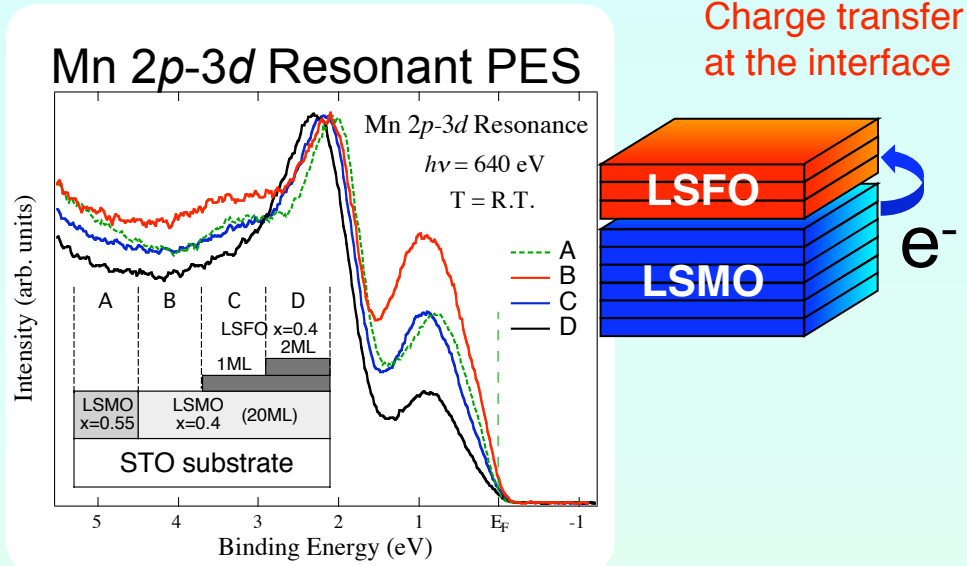
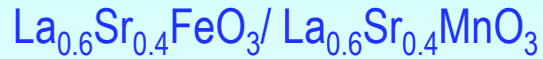
Nanodots&Nanowires



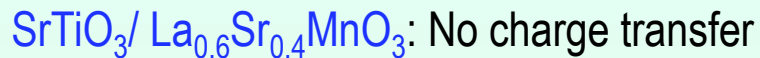
N. Nakagawa *et al.*, Jpn. J. Appl. Phys. **41**, L302 (2002)

In-situ PES on Oxide Superstructures

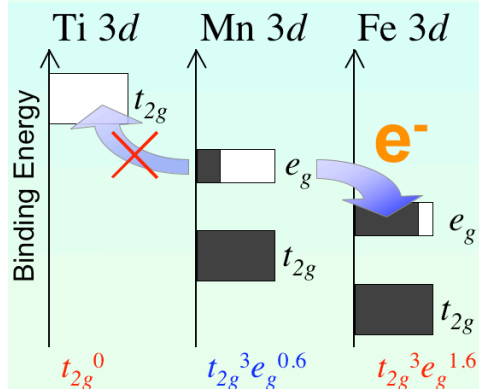
Charge transfer at heterointerfaces



H. Kumigashira *et al.*, *Appl. Phys. Lett.* **88**, 192504 (2006).

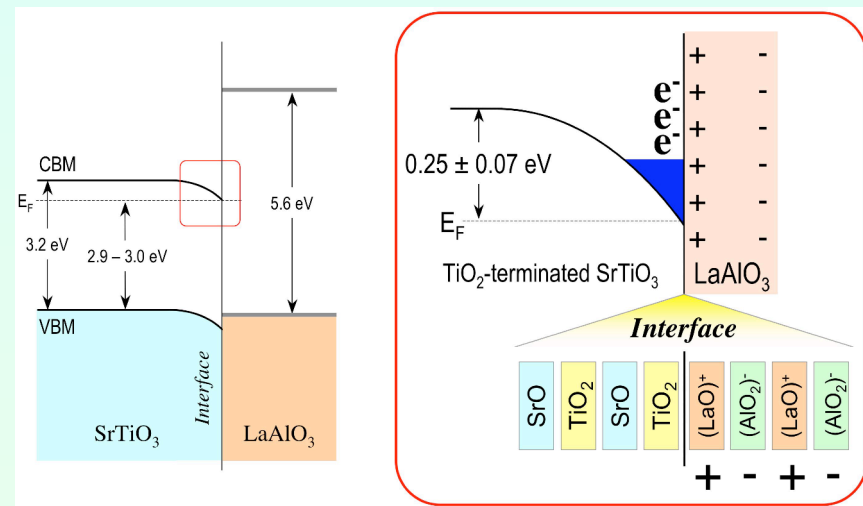
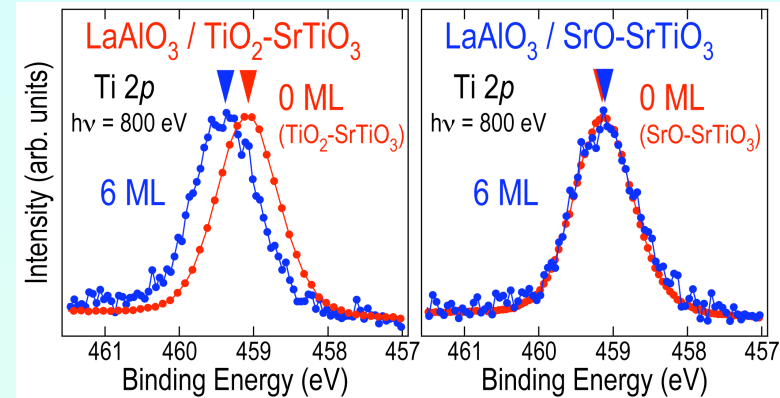


H. Kumigashira *et al.*, *Appl. Phys. Lett.* **84**, 5353 (2004).



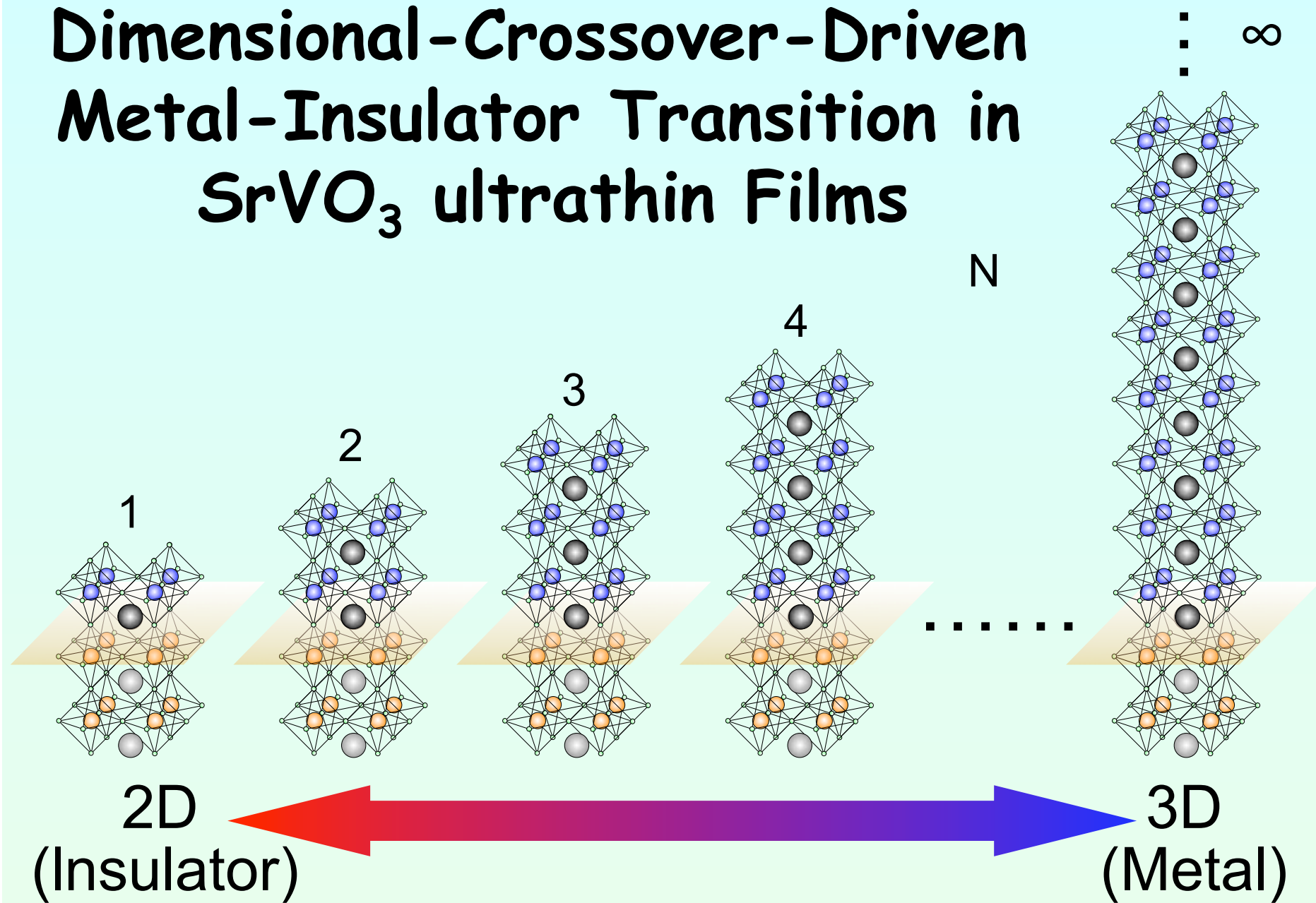
Charge redistribution at the interface is dominated by the difference of 3d energy levels among transition metals.

Origin of metallic conductivity at the $\text{LaAlO}_3 / \text{SrTiO}_3$ interface



K. Yoshimatsu, H.K. *et al.*, *Phys. Rev. Lett.* **101**, 026802 (08); *ibid* **102**, 199704 (2009).

Dimensional-Crossover-Driven Metal-Insulator Transition in SrVO_3 ultrathin Films



Metal Insulator Transition

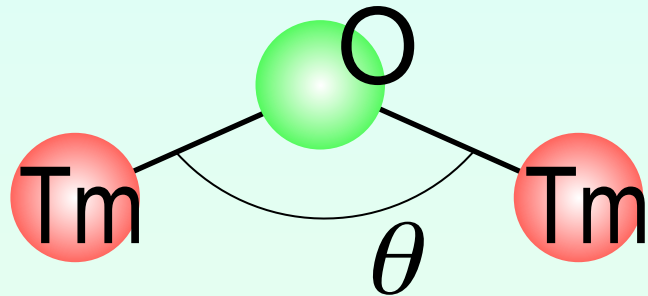
Mott-Hubbard theory

$U \gg W$ Insulator

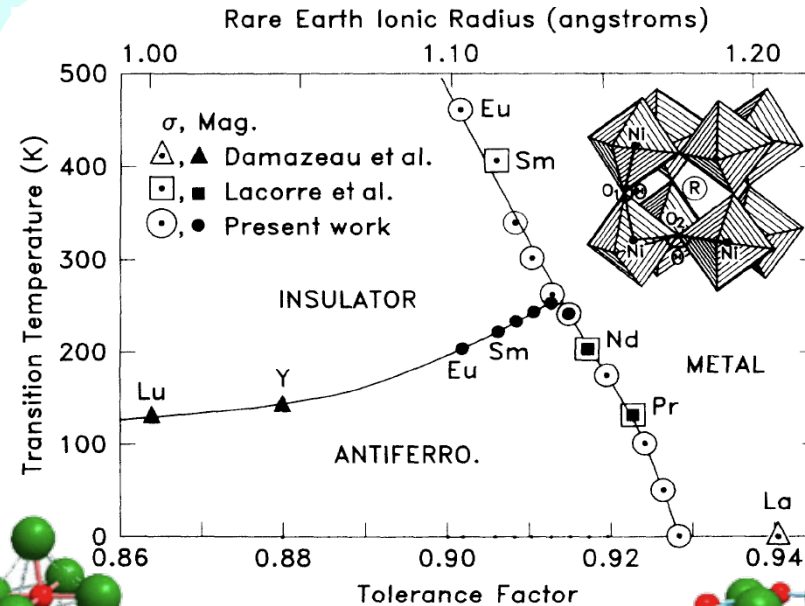
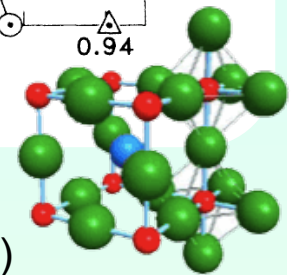
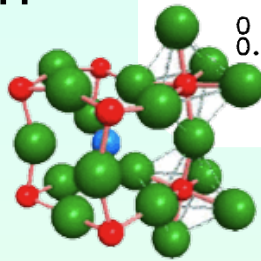
$U \ll W$ Metal

U : on-site Coulomb repulsion

W : one-electron band width



$$W \propto \cos^2 \theta$$



J.B. Torrance *et al.*,
Phys. Rev. B **45**, 8209 ('92)

For bulk materials, MIT has been intensively studied by chemical substitution of constituent ions with ones having a smaller ion radius. However, such chemical substitution always induce randomness in a solid.

Our Approach: Dimensional crossover occurring in an artificial structure

Digitally-controlled SrVO₃ ultrathin films

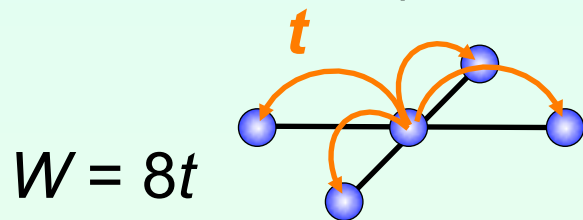
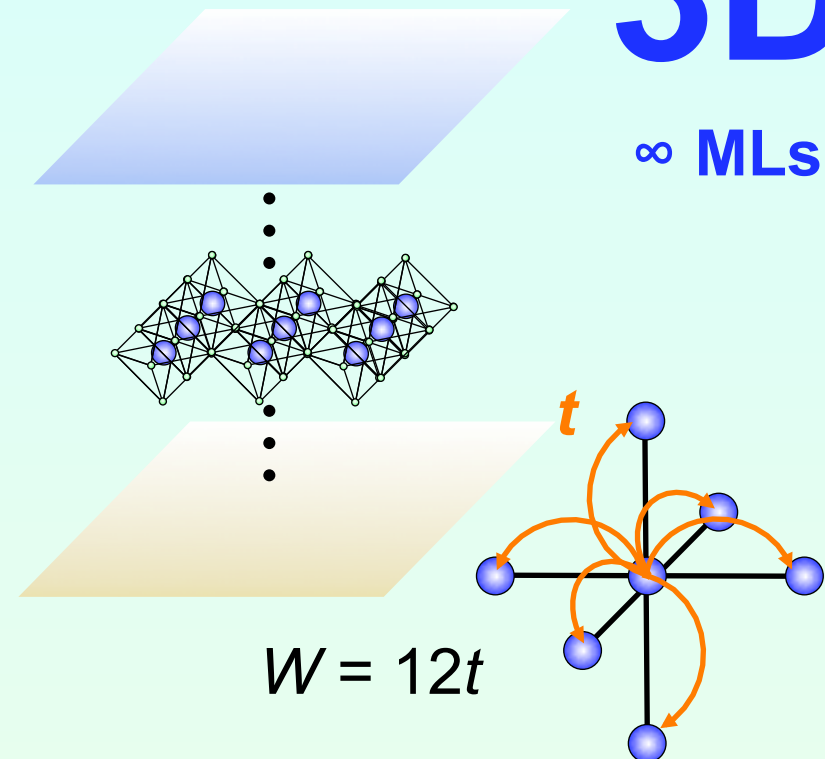
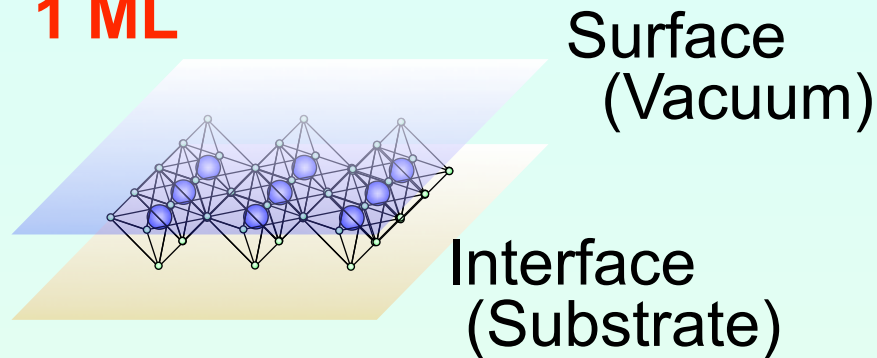
2D

SrVO₃: Paramagnetic metal
3d¹ system

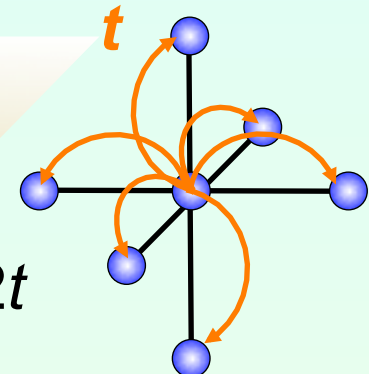
3D

1 ML

∞ MLs



$W = 12t$



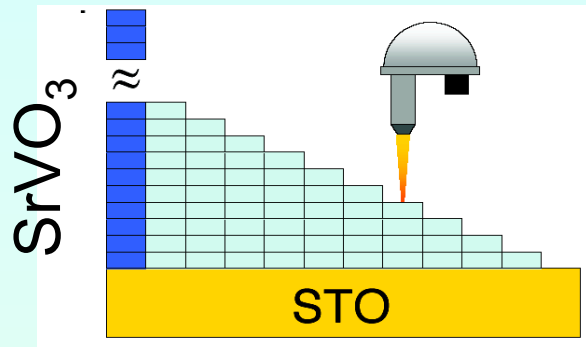
Dimensional crossover from 3D to 2D

Insulator

Metal

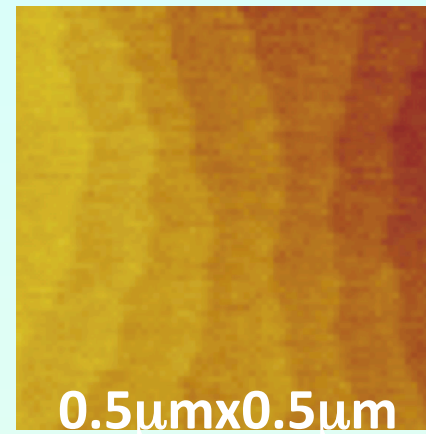
Atomically-flat Surface and Abrupt Interface

Preconditions to thickness dependent experiments

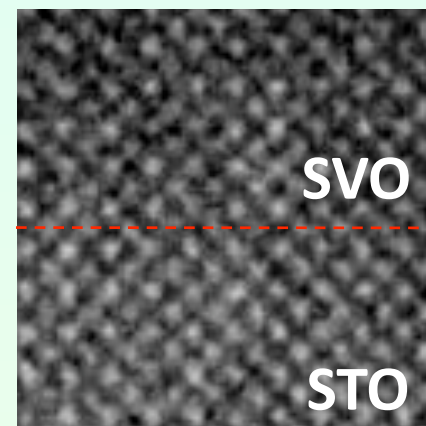


- ✓ Atomically flat surface (AFM image)
- ✓ Chemically abrupt interface (TEM image)
- ✓ Coherent growth of thin film (Reciprocal space mapping)

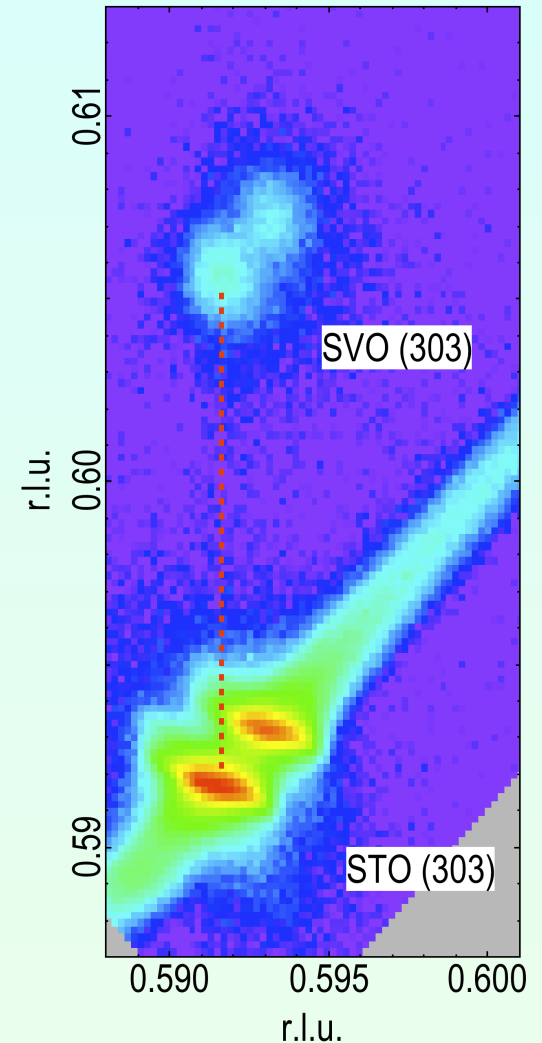
AFM image



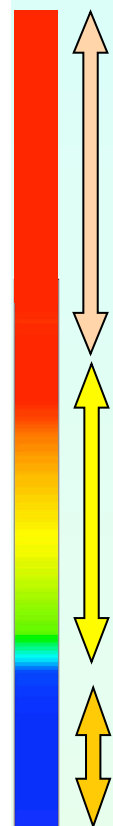
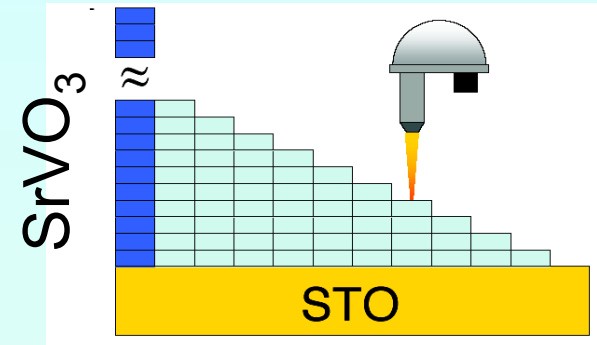
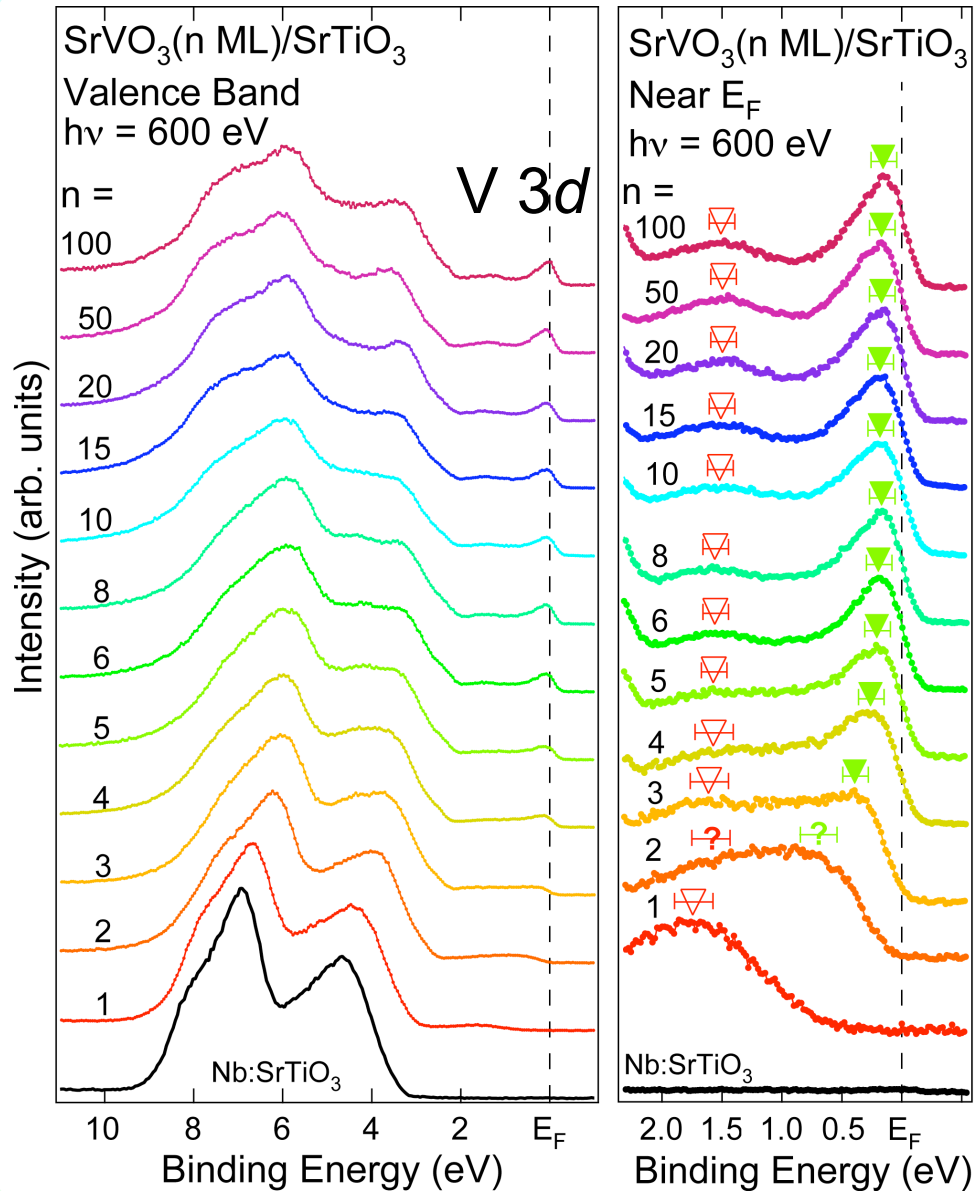
TEM image



4cXRD RSM around (303)



In situ PES Spectra of SrVO₃ thin Films



Spectra remain unchanged down to 6–8 ML

Pseudogap formation at E_F

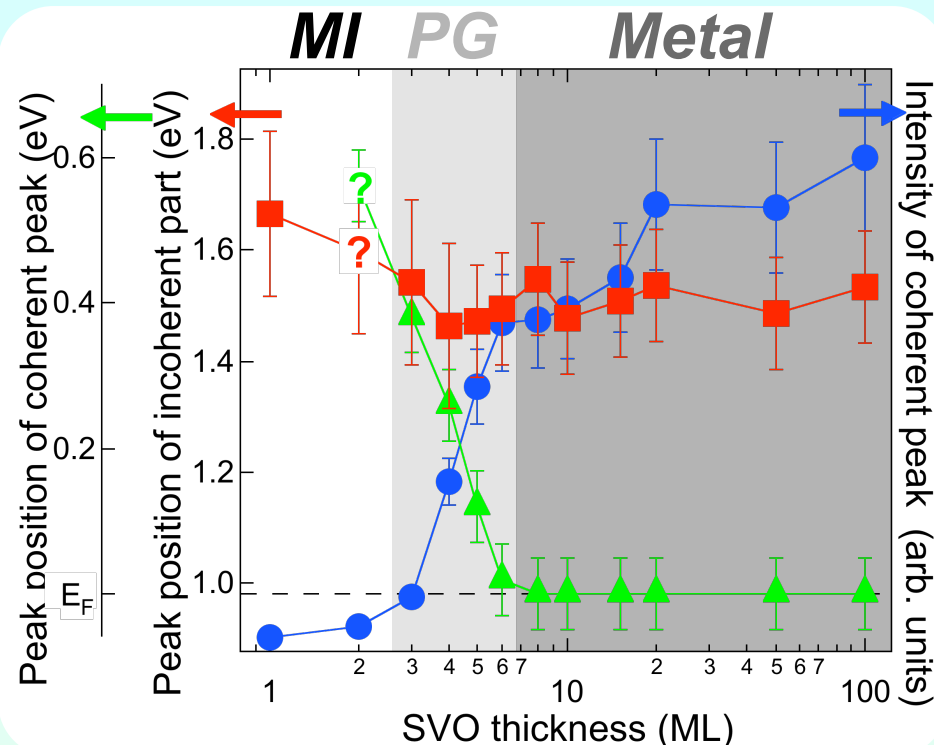
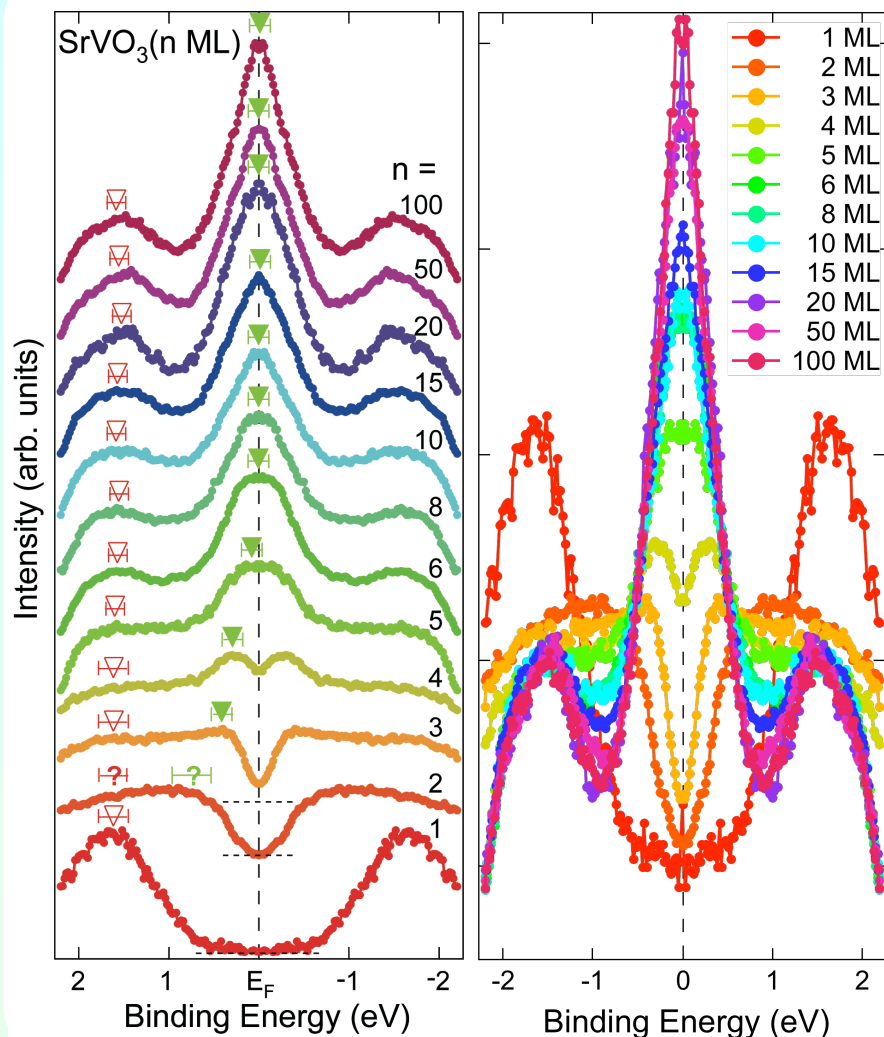
Disappearance of Fermi edge

MIT@2-3 ML

Gap at E_F

Metal-insulator transition occurs in the SVO thickness of 2-3 ML.

Dimensional-Crossover-Driven MIT in SrVO₃ Films

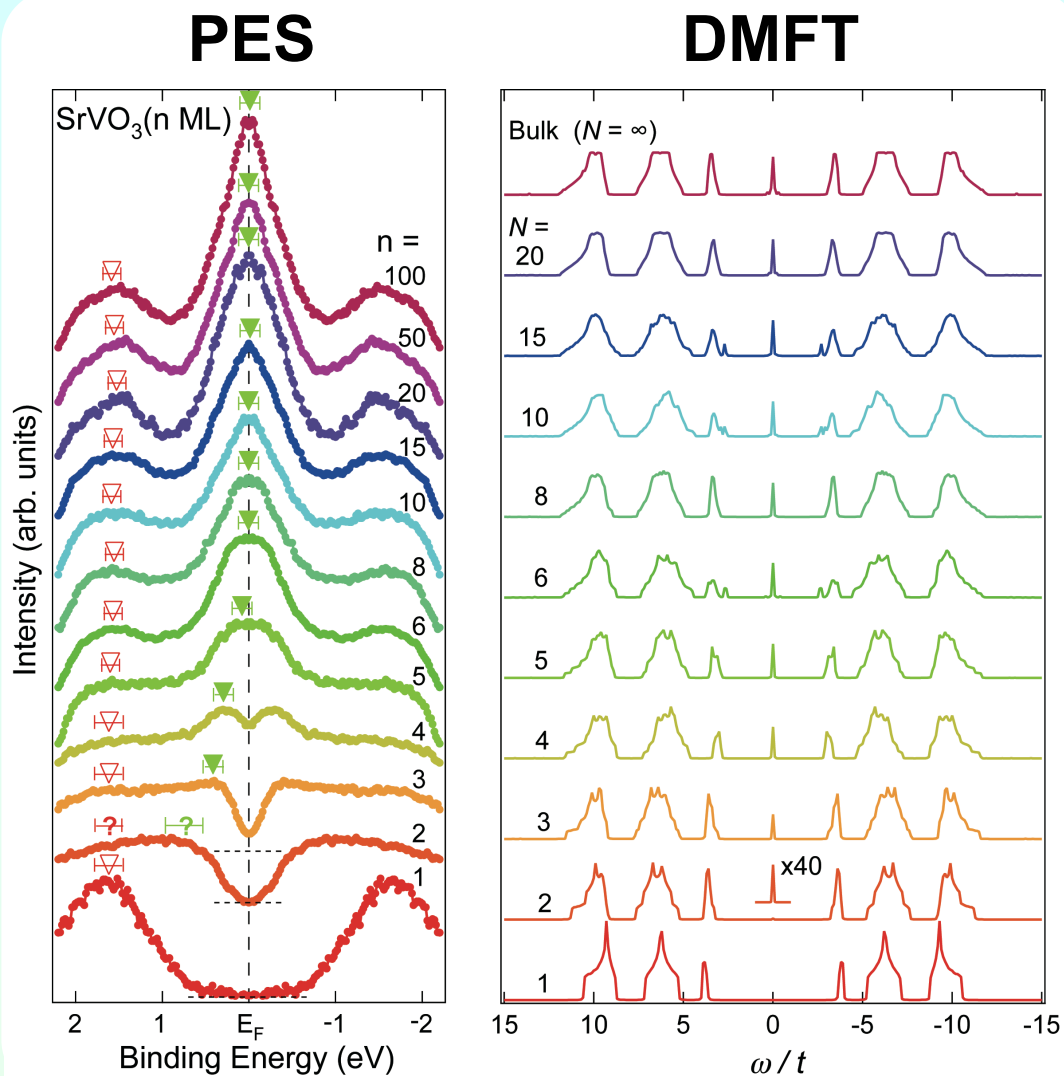


Quasiparticle peak intensity steeply increasing with increasing film thickness (W increasing).

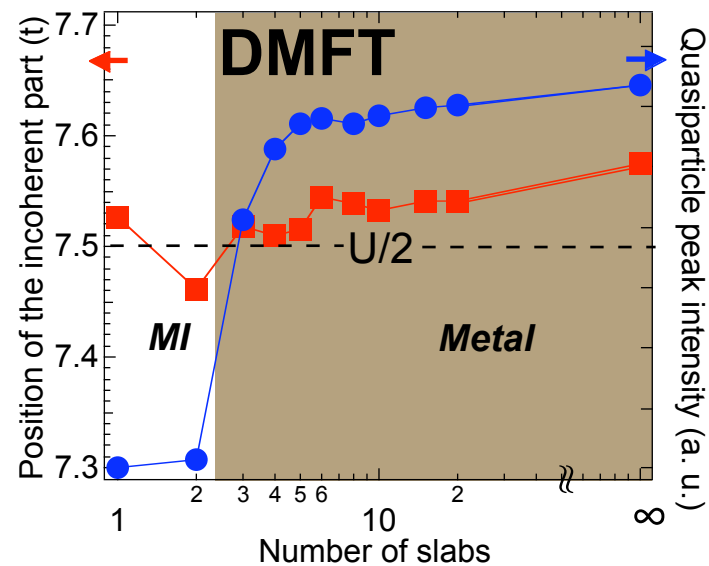
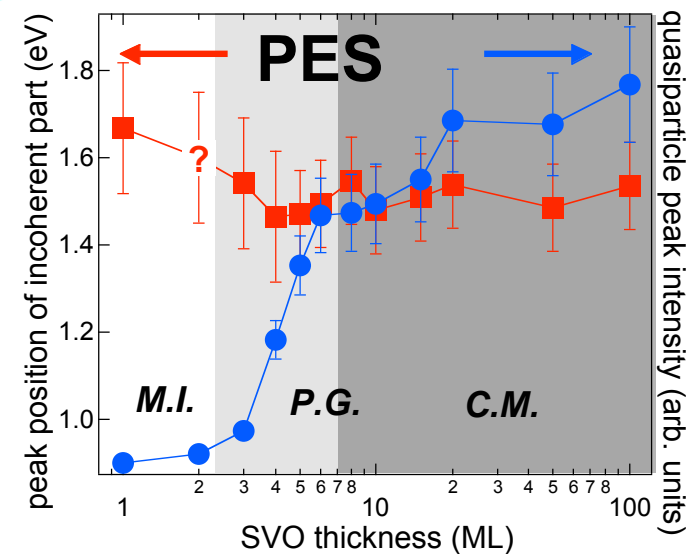
Peak position of the incoherent peak remains unchanged (U is constant).

Dimensional-Crossover-Driven (from 3D to 2D) MIT in SrVO₃ Ultrathin Films

Comparison between PES and Layer DMFT Cal.



K. Yoshimatsu, H.K., *et al.*, Phys. Rev. Lett. **104**, 147601 ('10).



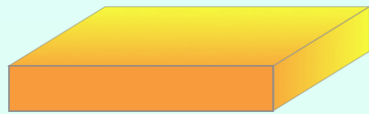
Spectral behavior is well reproduced by layer DMFT calculation.

Layer DMFT Calculations for Simulating the Dimensional-Crossover-Driven MIT

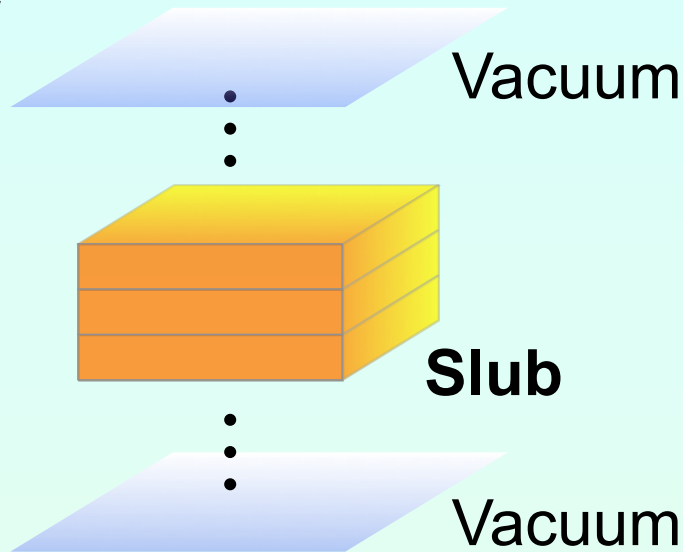
Multilayered single-band Hubbard model

2D

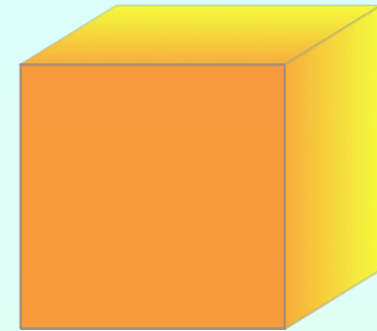
$$U = 15t$$



MIT at $U = 13t$ in 2D

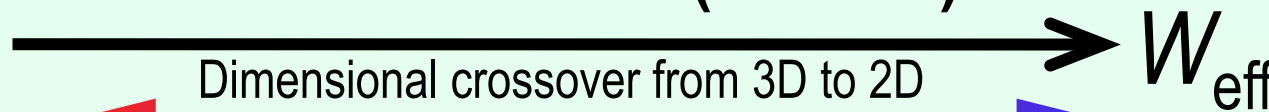


3D



MIT at $U = 16t$ in 3D

Number of slubs ($1 \leq N \leq 20$)



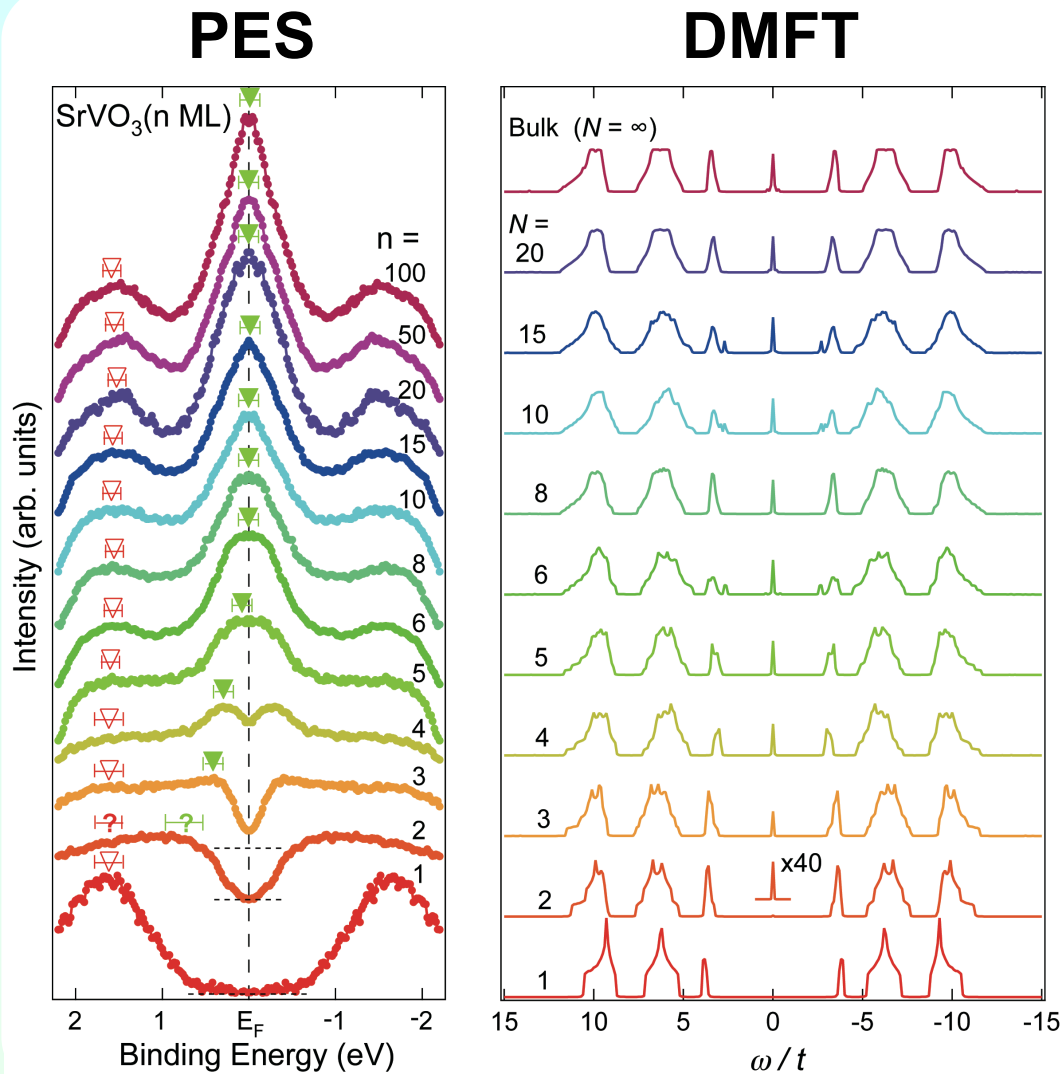
Insulator



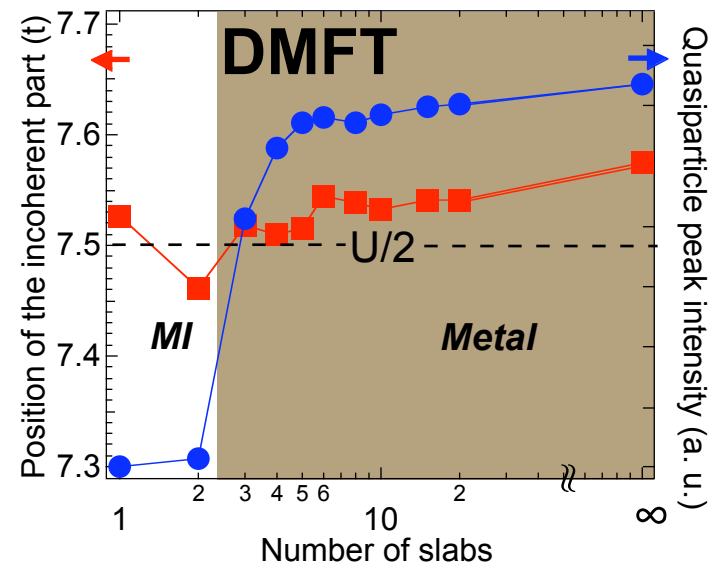
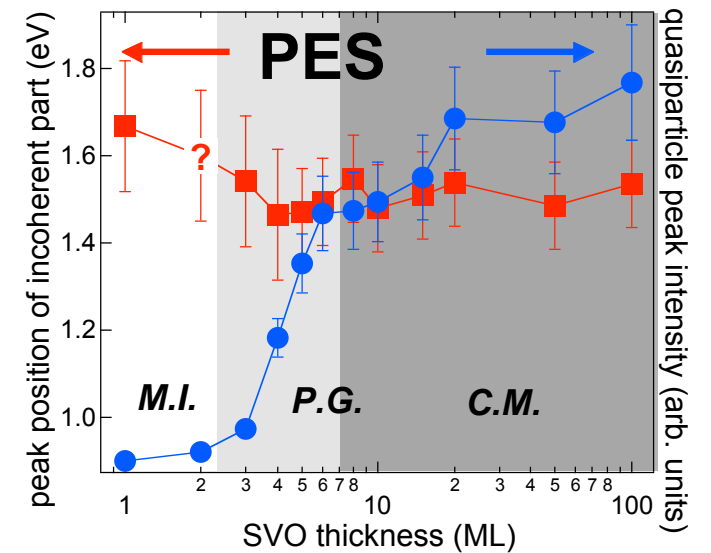
Metal

The system interpolates the two limits by changing the slab number corresponding to the change in the effective bandwidth (W_{eff}).

Comparison between PES and Layer DMFT Cal.



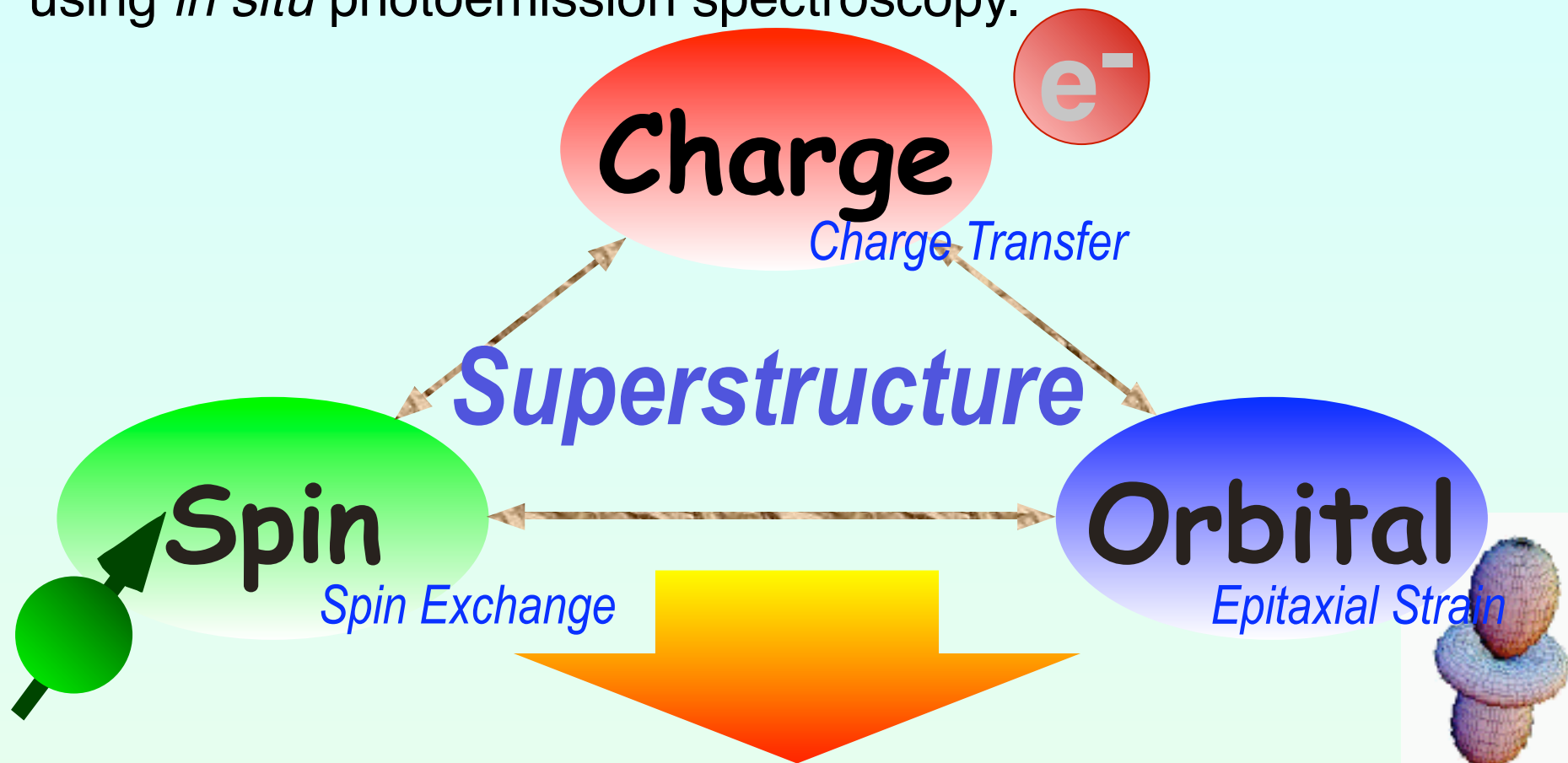
K. Yoshimatsu, H.K., *et al.*, Phys. Rev. Lett. **104**, 147601 ('10).



Dimensional-crossover-driven MIT in an SrVO₃ ultrathin films

Concluding Remarks

We studied the electronic states of oxide superstructures by using *in situ* photoemission spectroscopy.

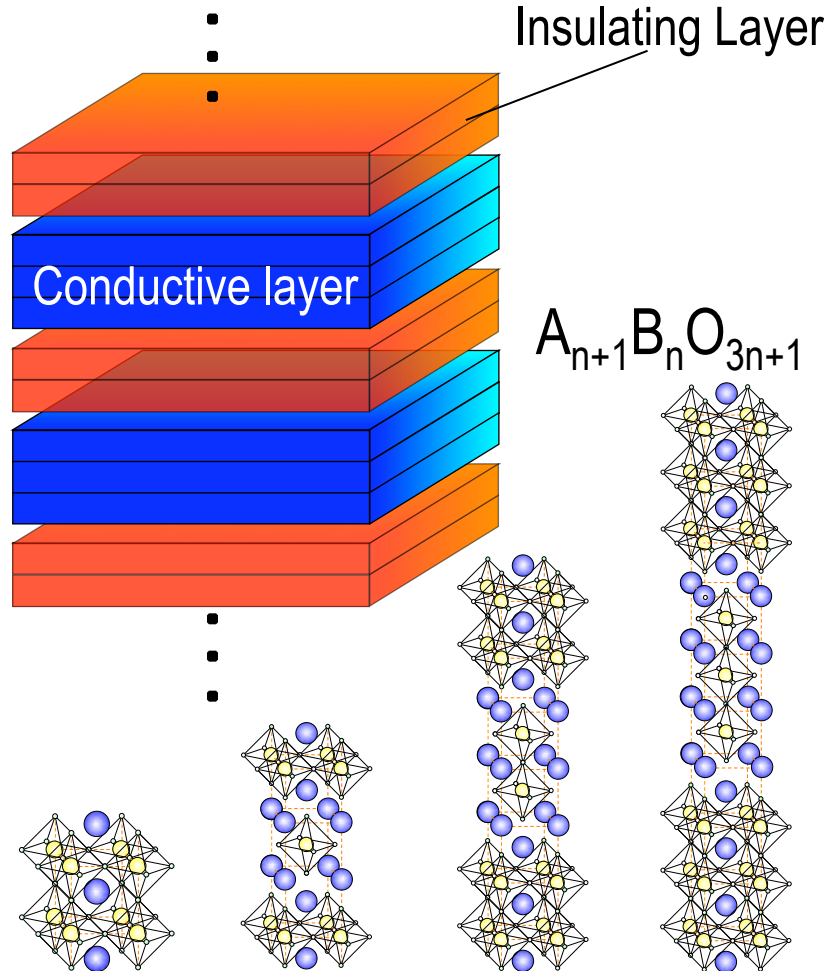


Photoemission studies using oxide superstructures enable us to pave a new way for the better understanding of the physics of strongly correlated oxides.

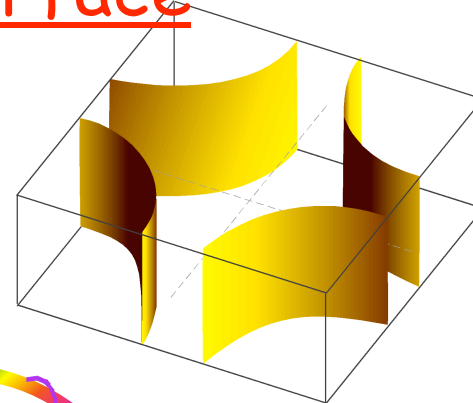
Outlooks

Fermiology of Quantum Well States in Artificial Structures Based on Strongly Correlated Oxides

Layered Oxides



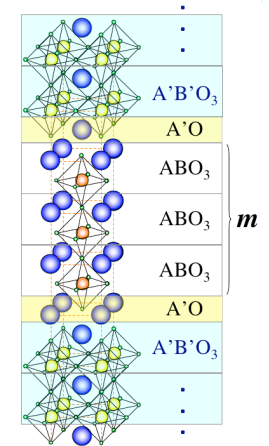
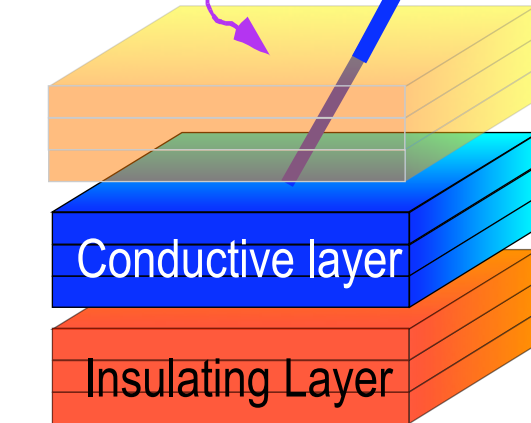
2D Fermi Surface



ARPES

S. R.

e^-



Oxide Quantum Well